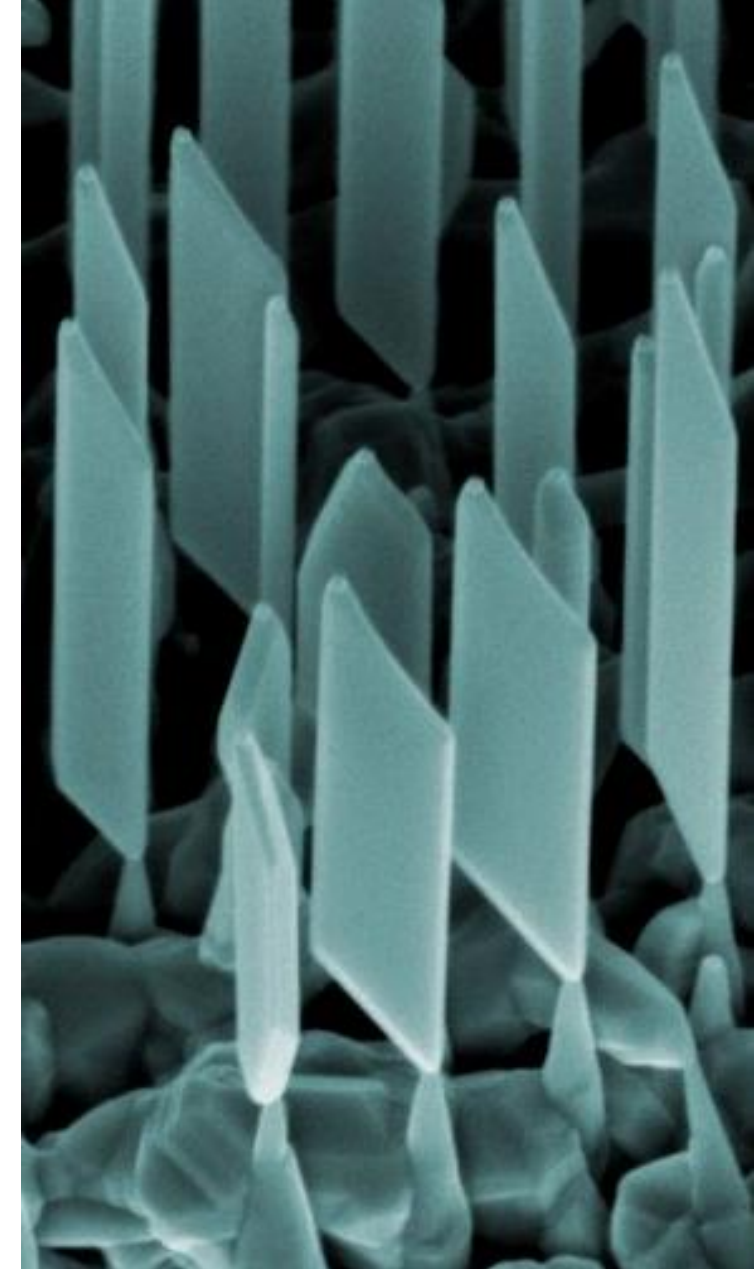




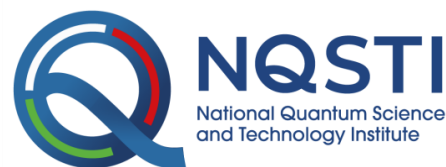
# Highly transmissive InSb nanoflag Josephson junctions

Stefan Heun

*NEST, Istituto Nanoscienze-CNR and Scuola Normale Superiore, Pisa, Italy*



AndQC



National Enterprise for nanoScience and nanoTechnology

NEST

# Outline of the talk

- InSb nanoflags for advanced devices
- Nanoflag-based Josephson junctions
- Josephson diode effect in InSb nanoflags
- Half-integer Shapiro steps in InSb nanoflags

# Outline of the talk

- **InSb nanoflags for advanced devices**
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- Josephson diode effect in InSb nanoflags
- Half-integer Shapiro steps in InSb nanoflags

# InSb is appealing for spintronics

Small bandgap  $E_g = 0.23 \text{ eV}$

Low effective mass  $m/m_0 = 0.018$

Strong SOC  $E_{\text{SOC}} \sim 200 \mu\text{eV}$

# InSb is appealing for spintronics but challenging to grow 2D



Lucia Sorba

Small bandgap

$$E_g = 0.23 \text{ eV}$$

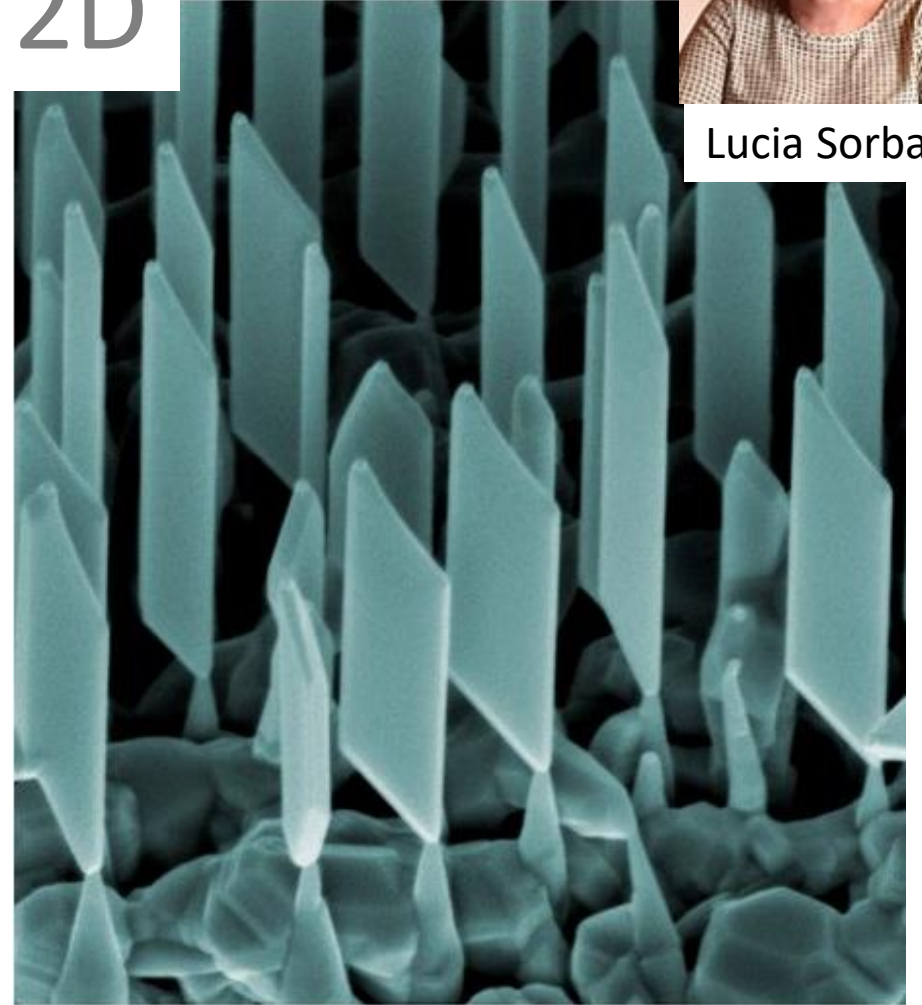
Low effective mass

$$m/m_0 = 0.018$$

Strong SOC

$$E_{\text{SOC}} \sim 200 \text{ } \mu\text{eV}$$

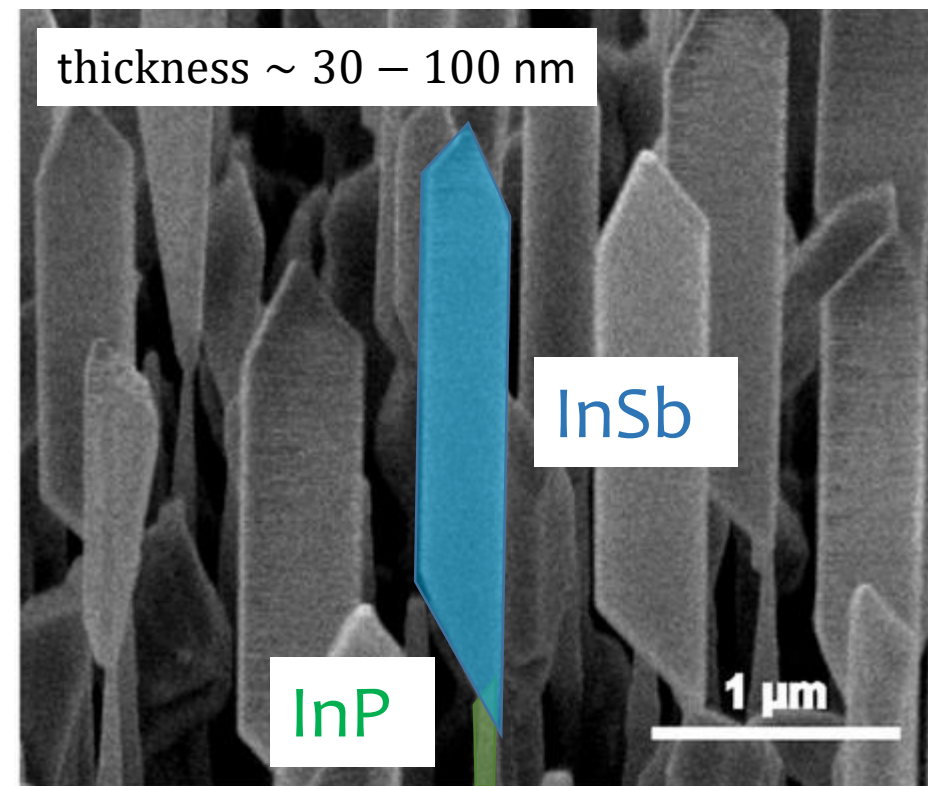
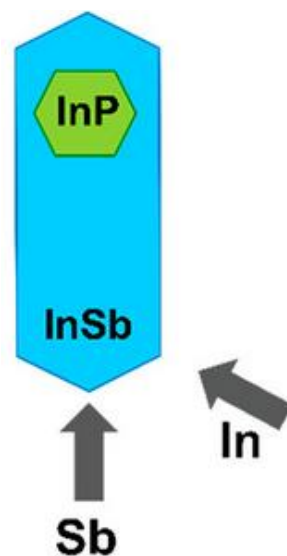
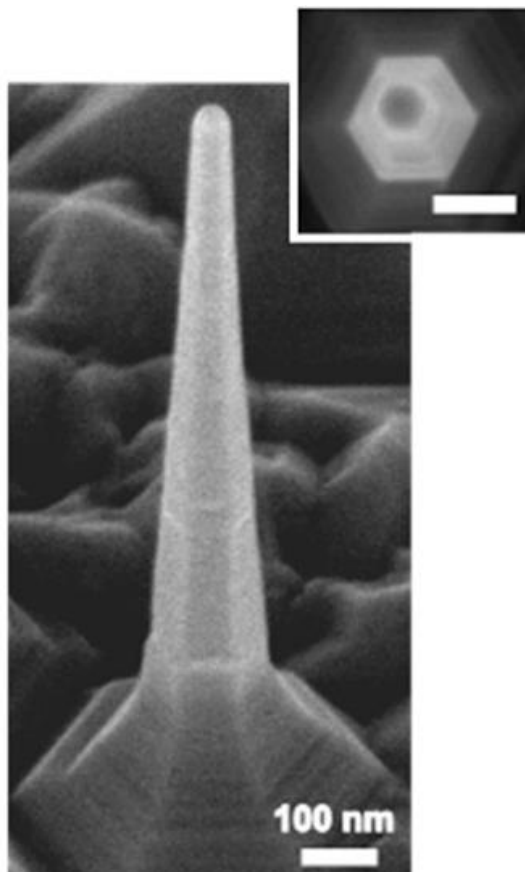
High-mobility 2D nanostructures



# Nanoflags are grown via Chemical Beam Epitaxy



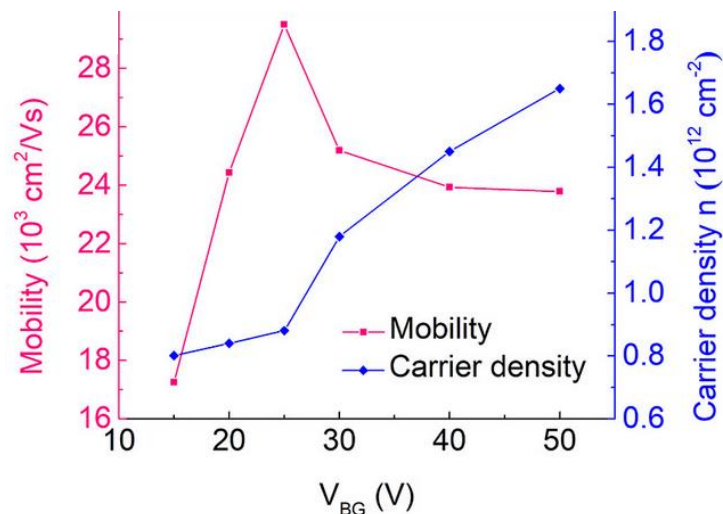
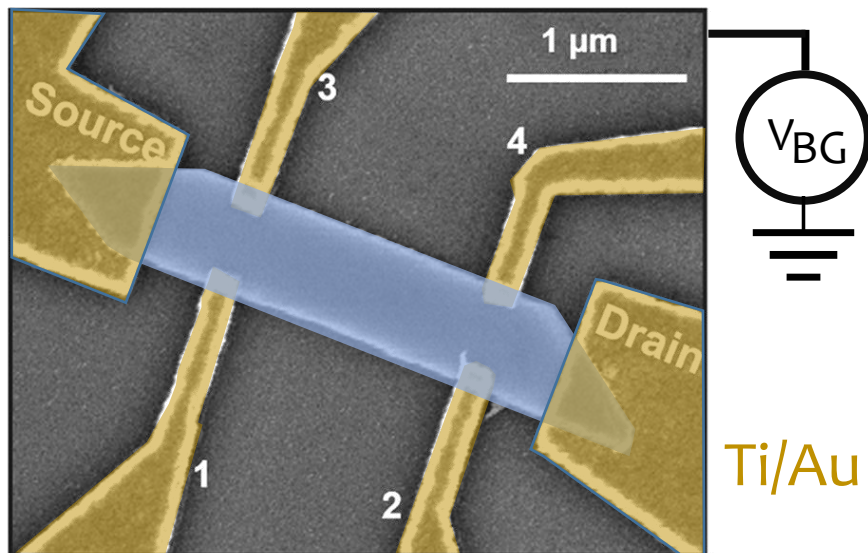
Isha Verma



Defect-free InSb zinc blende lattice

# NFs show high mobility and giant $g^*$ -factor

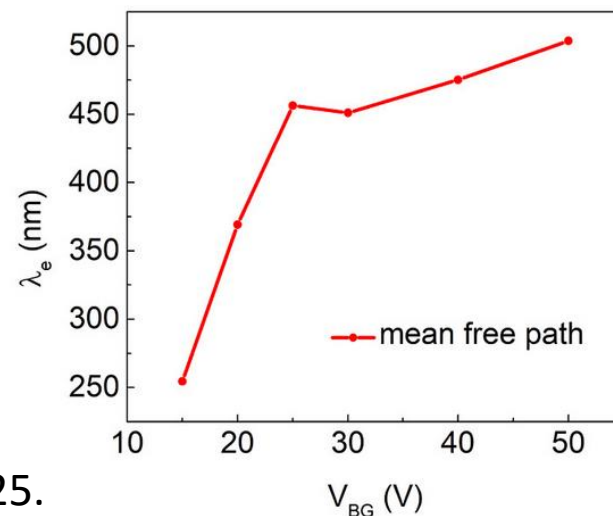
@ T = 4.2 K



$$\mu_e \sim 29500 \text{ cm}^2/\text{Vs}$$

@ T = 250 mK

$$g^* \sim 44$$



$$\lambda_{\text{mfp}} \sim 500 \text{ nm}$$

# Outline of the talk

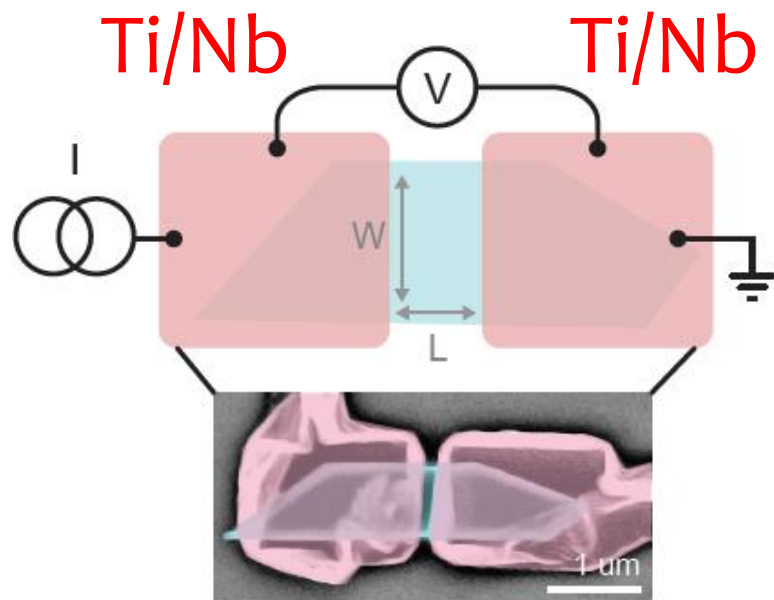
- InSb nanoflags for advanced devices
- **Nanoflag-based Josephson junctions**
- Josephson diode effect in InSb nanoflags
- Half-integer Shapiro steps in InSb nanoflags



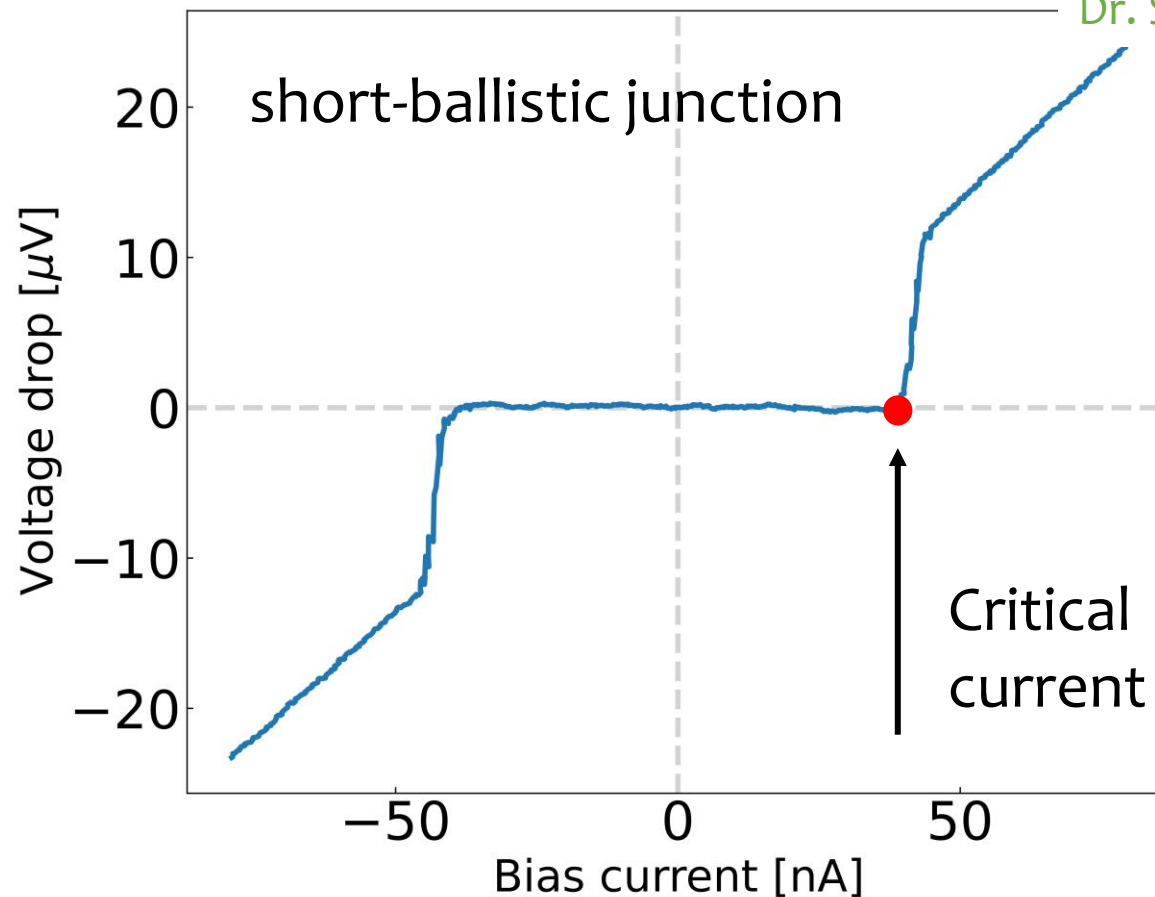
# The devices show supercurrent



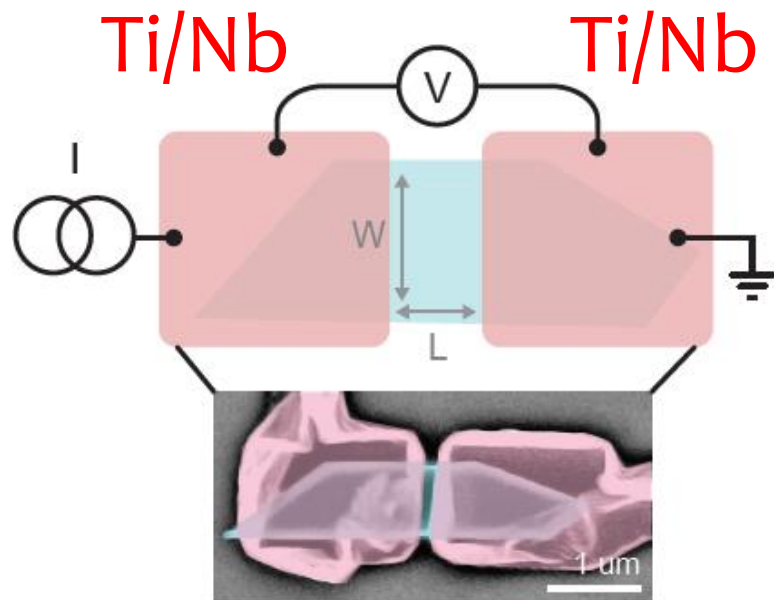
Dr. S. Salimian



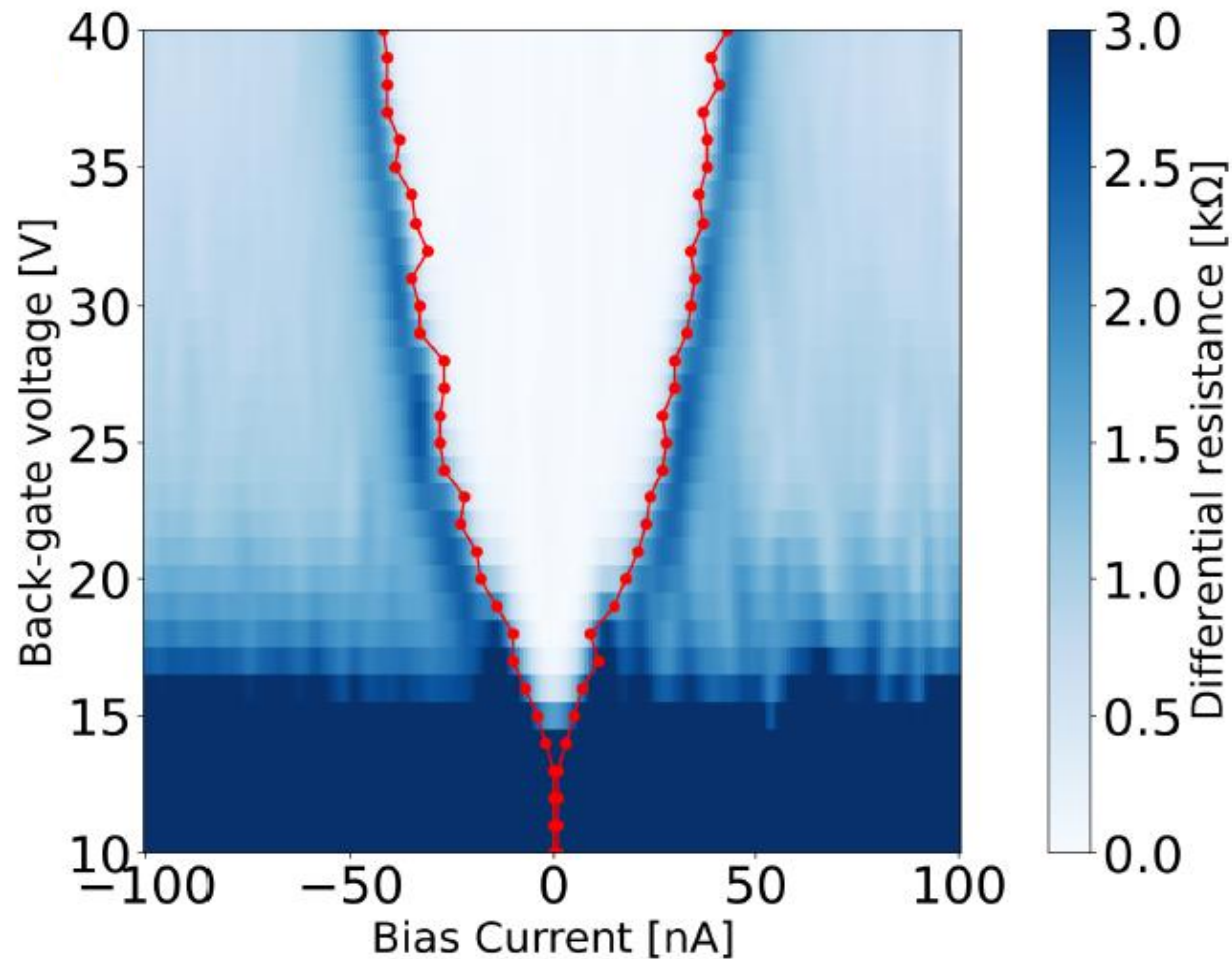
$\lambda_{\text{mfp}}$	500 nm
L	200 nm
$\xi_S$	750 nm



# The devices show gate-tunable supercurrent

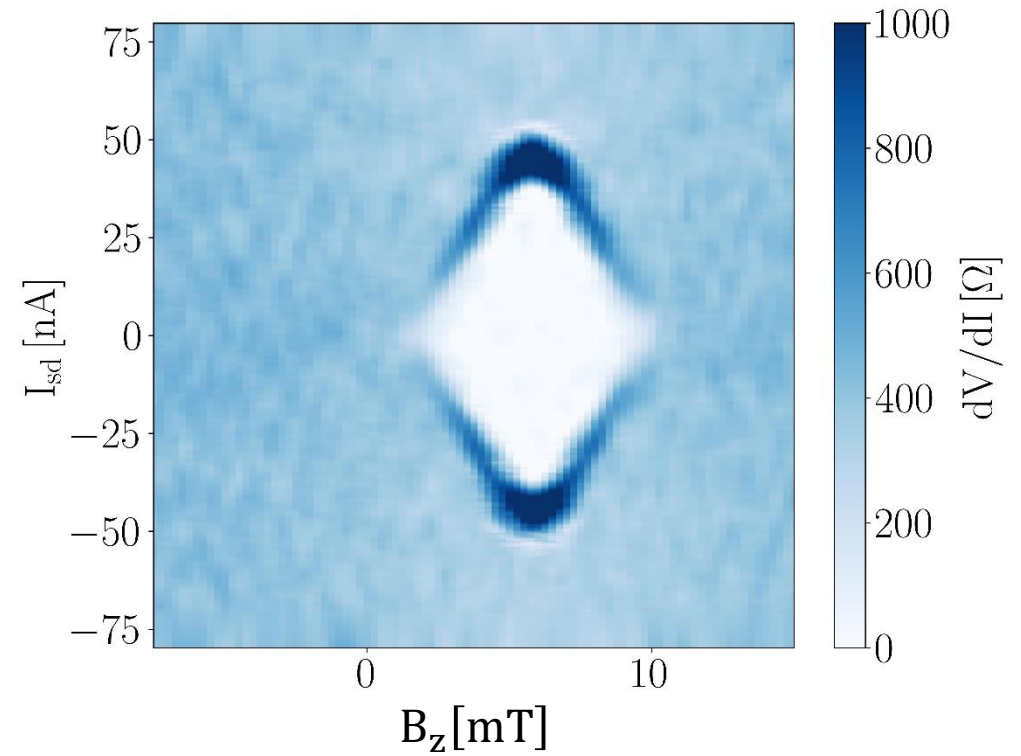
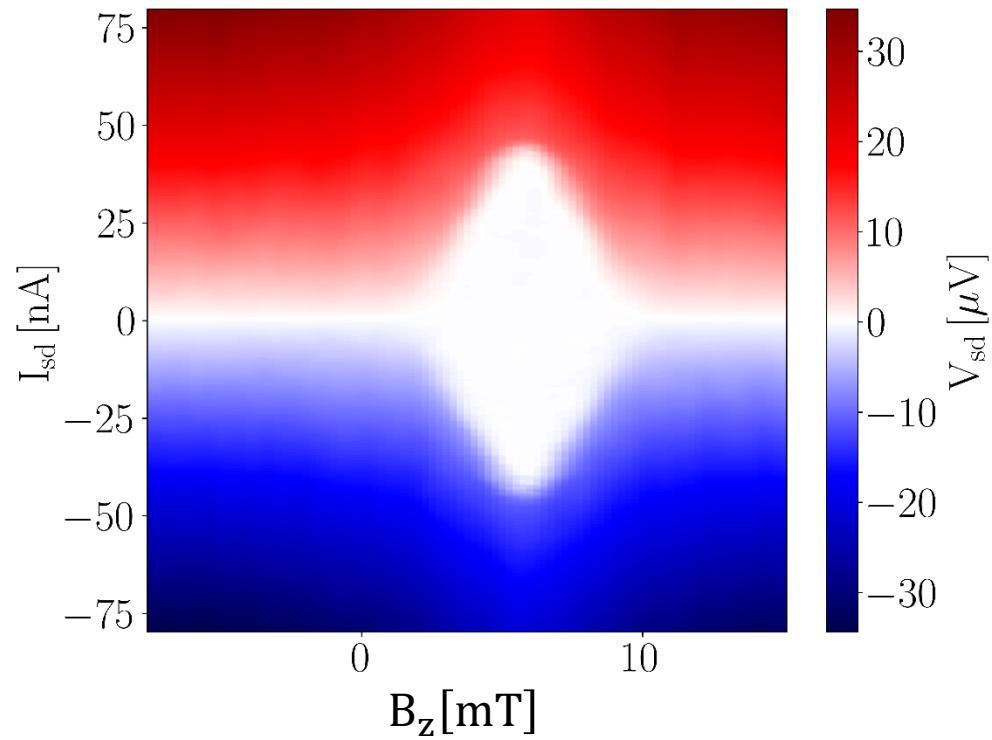


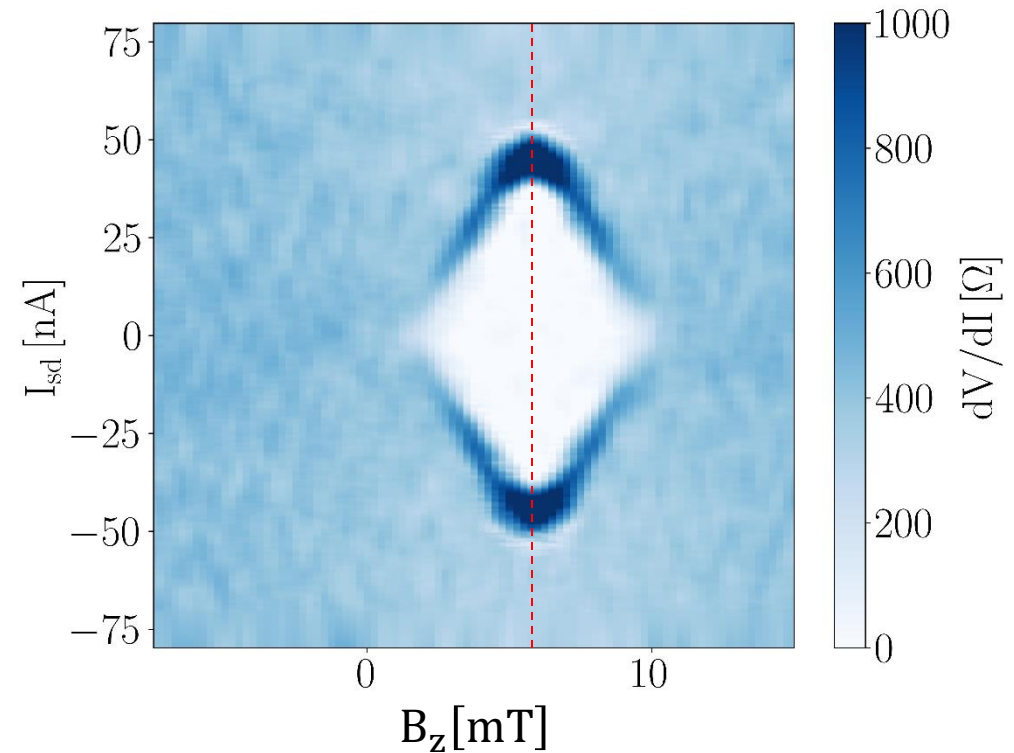
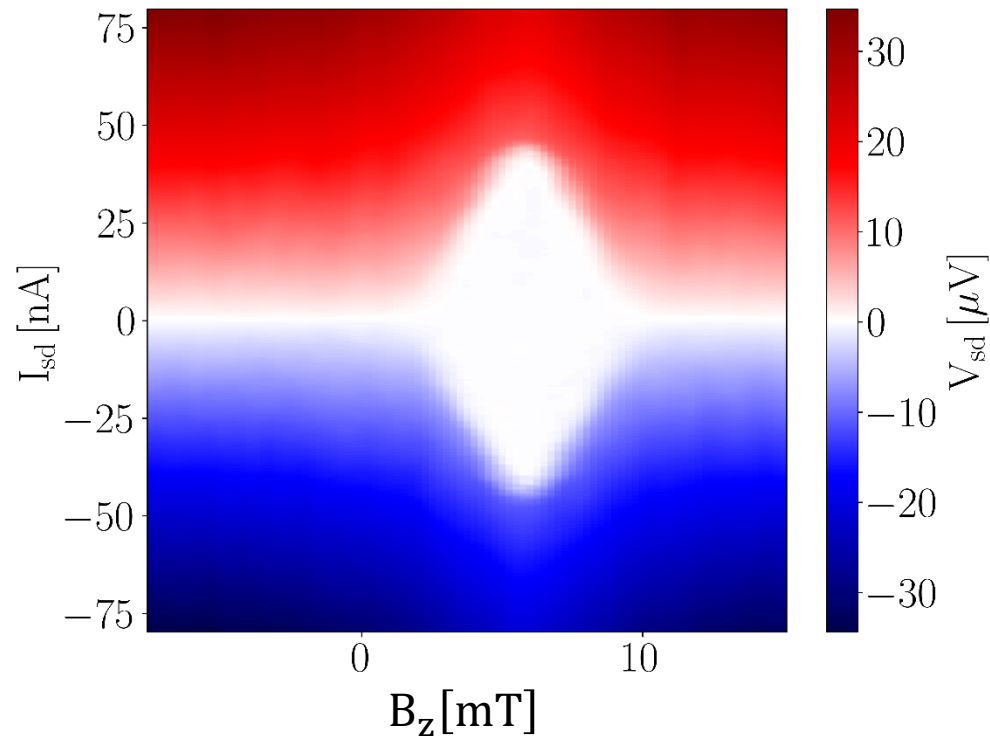
$\lambda_{\text{mfp}}$	500 nm
$L$	200 nm
$\xi_S$	750 nm



# Magnetic Interference Pattern

$T = 250 \text{ mK}$



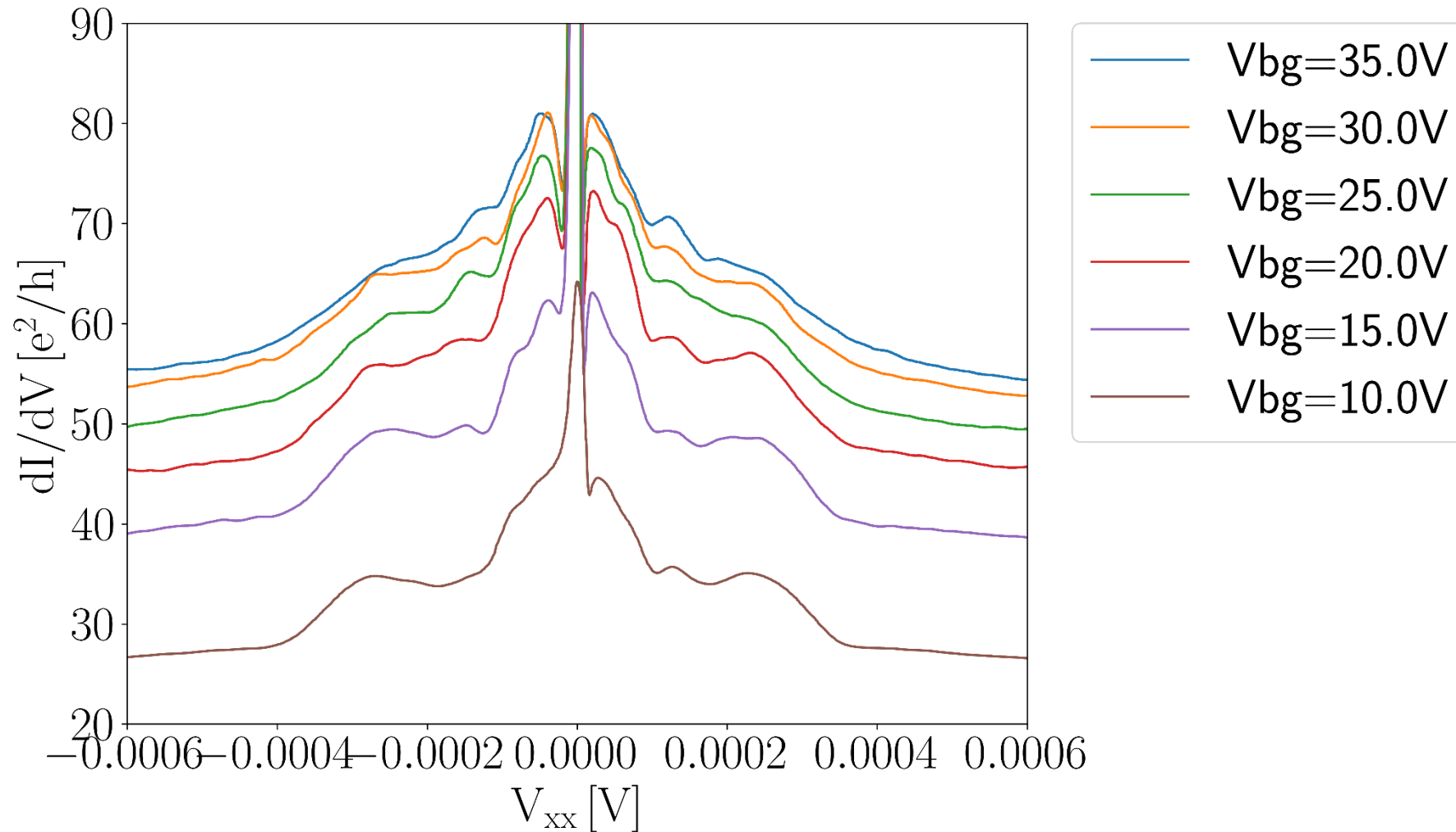


Why no sides lobes in the Fraunhofer pattern?

- Even-odd effect? (de Vries et al., Phys. Rev. Res. 1 (2019) 032031)
- Narrow junction? (Cuevas & Bergeret, Phys. Rev. Lett. 99 (2007) 217002)

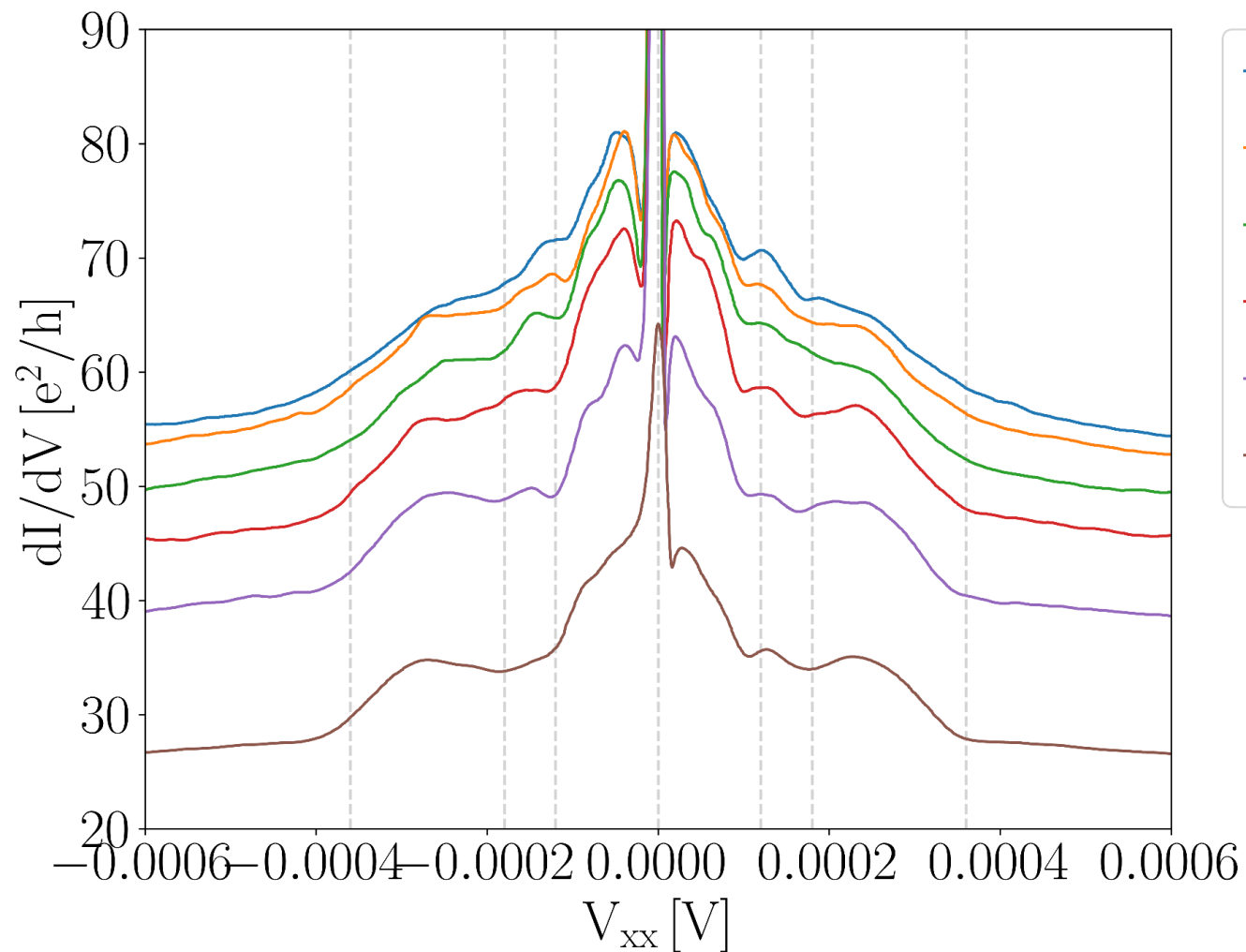
# Multiple Andreev Reflections

$T = 250 \text{ mK}$



# Multiple Andreev Reflections

$T = 250 \text{ mK}$



- $V_{bg}=35.0\text{V}$
- $V_{bg}=30.0\text{V}$
- $V_{bg}=25.0\text{V}$
- $V_{bg}=20.0\text{V}$
- $V_{bg}=15.0\text{V}$
- $V_{bg}=10.0\text{V}$



*Michal P. Nowak*

$$eV(n) = 2\Delta^*/n \quad (n=1, 2, 3 \dots)$$

$$\Delta^* \sim 160 \mu\text{eV}$$

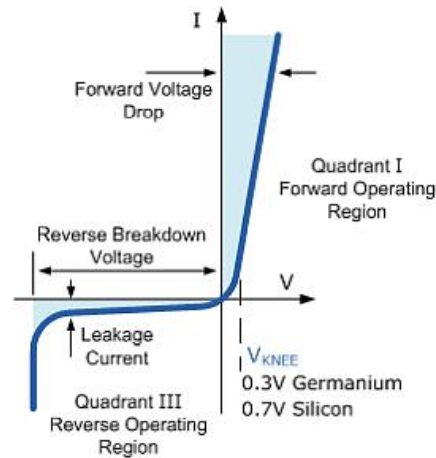
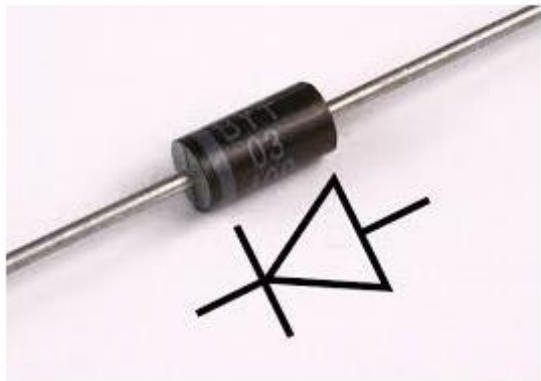
transparency  $\tau = 0.94$

# Outline of the talk

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- **Josephson diode effect in InSb nanoflags**
- Half-integer Shapiro steps in InSb nanoflags

# Non-reciprocal transport

## Semiconductor diode with pn-junction



The p-n junction is at the basis of classical electronics.

## Magneto-chiral anisotropy (MCA)

- Magneto-chiral anisotropy caused by breaking of spatial-inversion and time-reversal symmetries

- $R = R_0 [1 + \gamma \hat{e}_z (\mathbf{B} \times \mathbf{I})]$

- Elusive in CM systems

- $\gamma \sim \left( \frac{E_{SOI}}{E_F} \right) \sim 10^{-3} \text{ to } 10^{-2} \text{ T}^{-1} \text{ A}^{-1}$

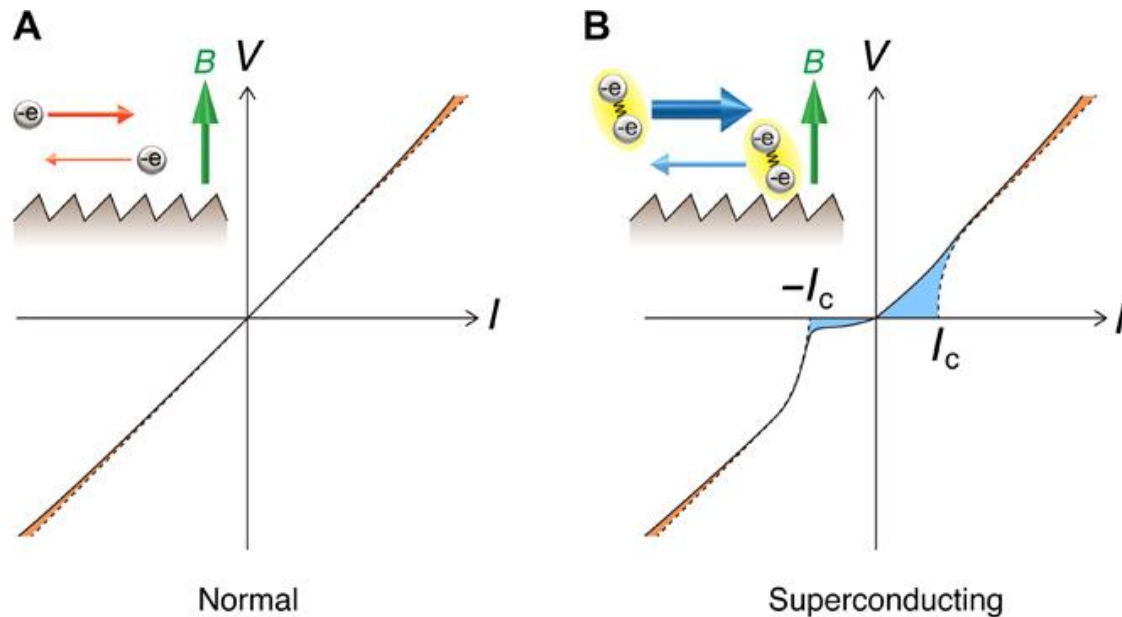


# MCA in superconductors

- Superconducting order defines a new energy scale:

$$E_F \gg \Delta \sim \text{meV}$$

- MCA is strongly enhanced ( $10^5$ ) in the resistive state
- What happens to the supercurrent?



**SUPERCURRENT DIODE EFFECT**

Article

## Observation of superconducting diode effect

<https://doi.org/10.1038/s41586-020-2590-4>

Received: 14 March 2020

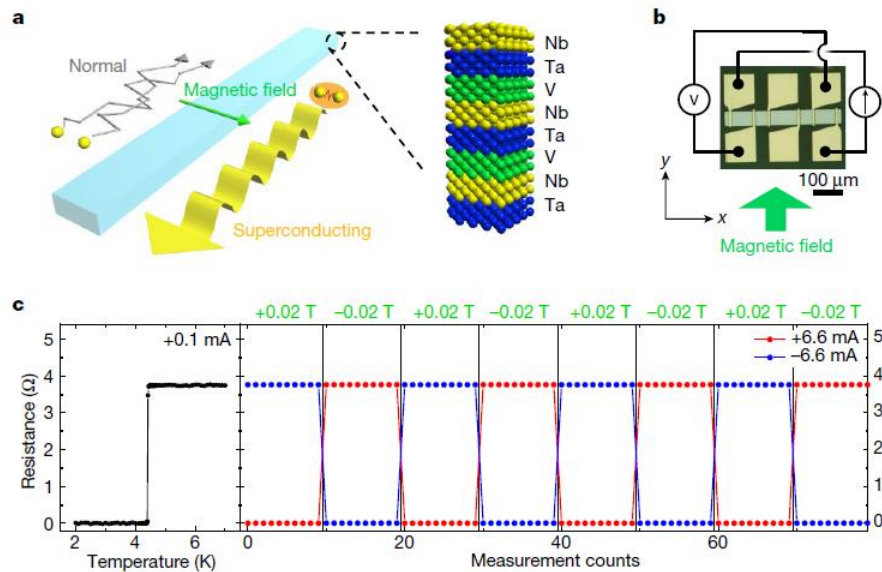
Accepted: 23 June 2020

Published online: 19 August 2020

Check for updates

Fuyuki Ando<sup>1</sup>, Yuta Miyasaka<sup>1</sup>, Tian Li<sup>1</sup>, Jun Ishizuka<sup>2</sup>, Tomonori Arakawa<sup>3,4</sup>, Yoichi Shiota<sup>1</sup>, Takahiro Moriyama<sup>1</sup>, Youichi Yanase<sup>2</sup> & Teruo Ono<sup>1,4</sup>✉

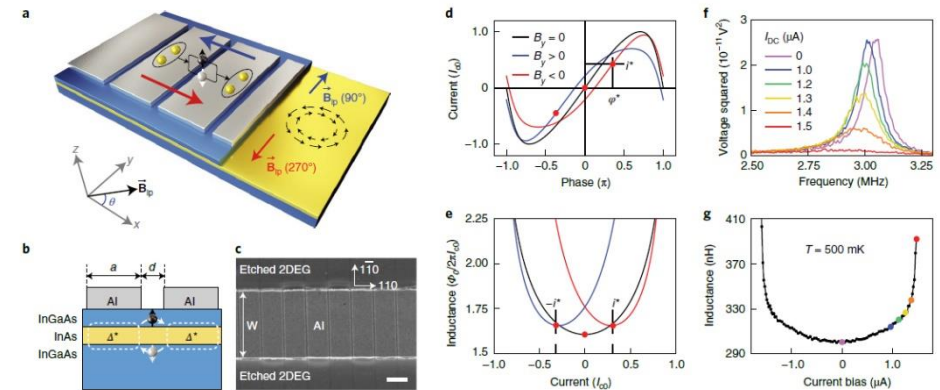
Nonlinear optical and electrical effects associated with a lack of spatial inversion symmetry allow direction-selective propagation and transport of quantum particles, such as photons<sup>1</sup> and electrons<sup>2–9</sup>. The most common example of such nonreciprocal



F. Ando et al., Nature 584 (2020) 373.

## Supercurrent rectification and magnetochiral effects in symmetric Josephson junctions

Christian Baumgartner<sup>1,8</sup>, Lorenz Fuchs<sup>1,8</sup>, Andreas Costa<sup>2</sup>, Simon Reinhardt<sup>1</sup>, Sergei Gronin<sup>3,4</sup>, Geoffrey C. Gardner<sup>3,4</sup>, Tyler Lindemann<sup>4,5</sup>, Michael J. Manfra<sup>3,4,5,6,7</sup>, Paulo E. Faria Junior<sup>2</sup>, Denis Kochan<sup>2</sup>, Jaroslav Fabian<sup>2</sup>, Nicola Paradiso<sup>1</sup>✉ and Christoph Strunk<sup>1</sup>



C. Baumgartner et al., Nat. Nano 17 (2022) 39.

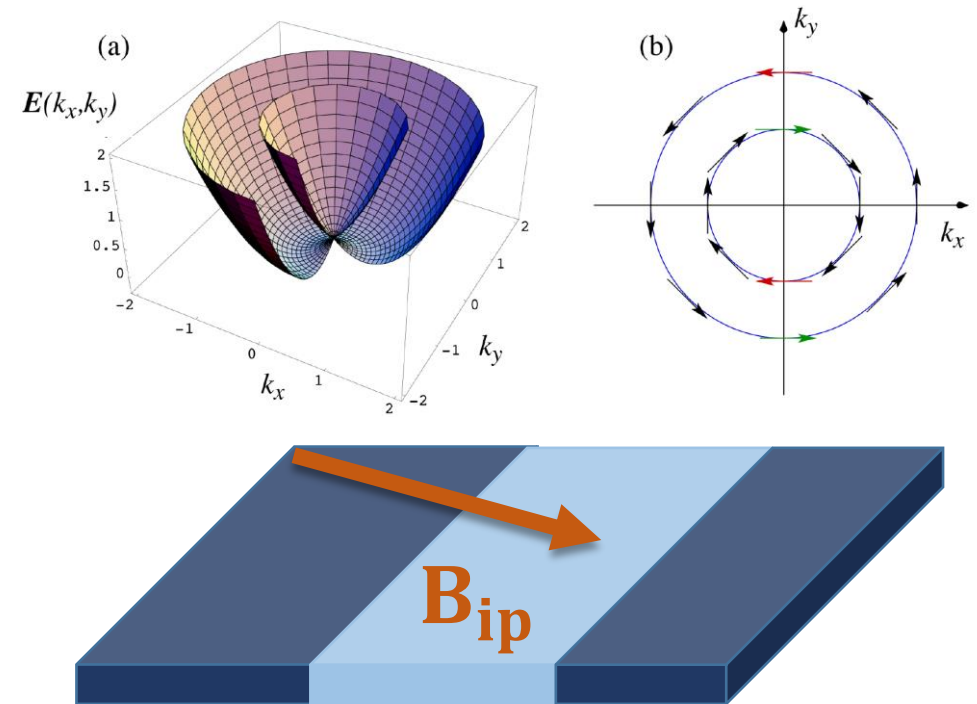
# Ingredients for intrinsic SDE

Requirements:

- Breaking of TR symmetry
- Breaking of I symmetry
- Robust superconducting order

Ideal candidate:  
strong SOI and large effective g-factor

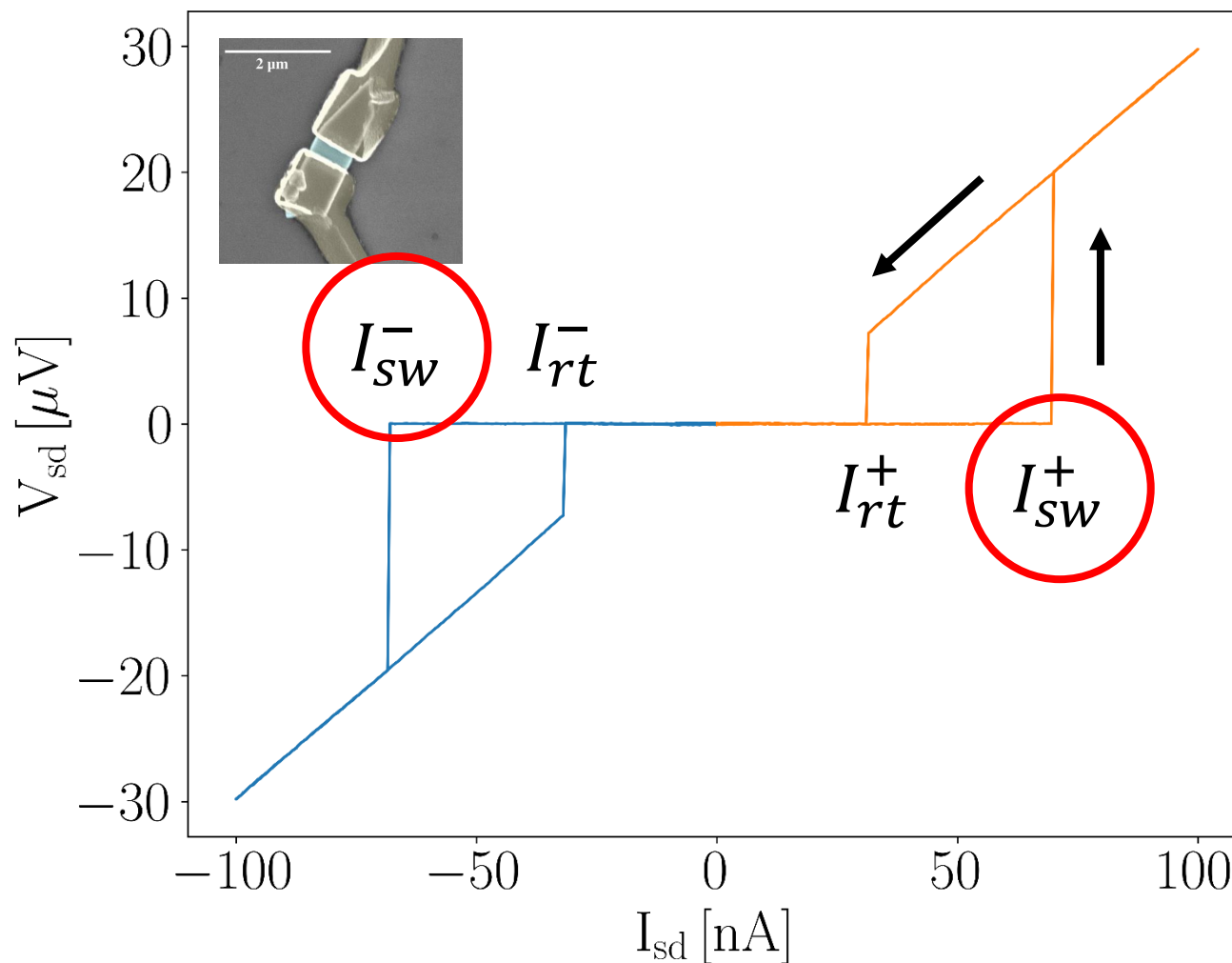
SNS junction + SOI + Zeeman field



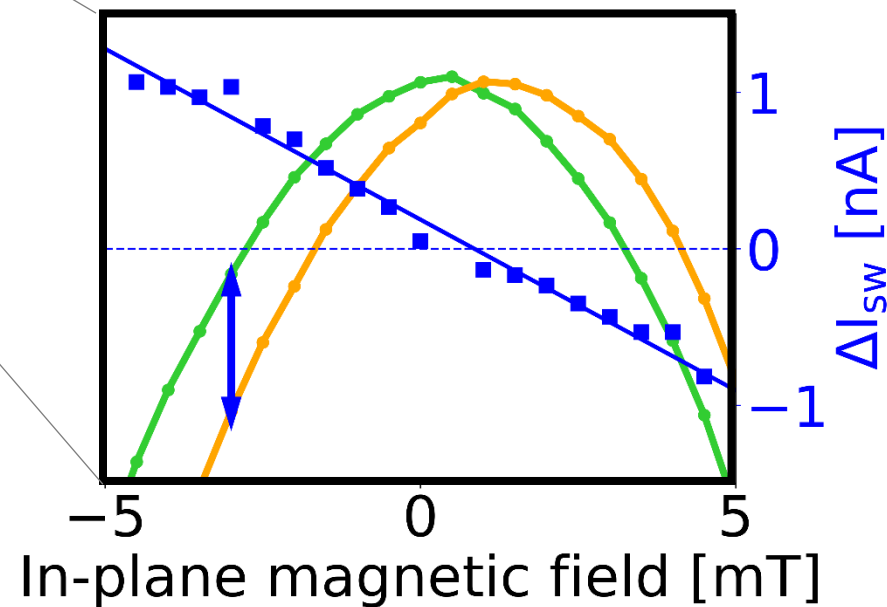
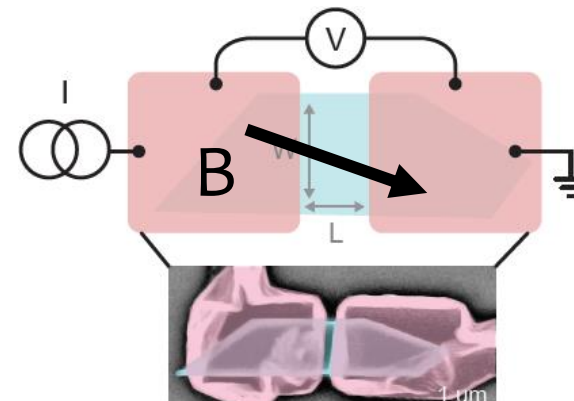
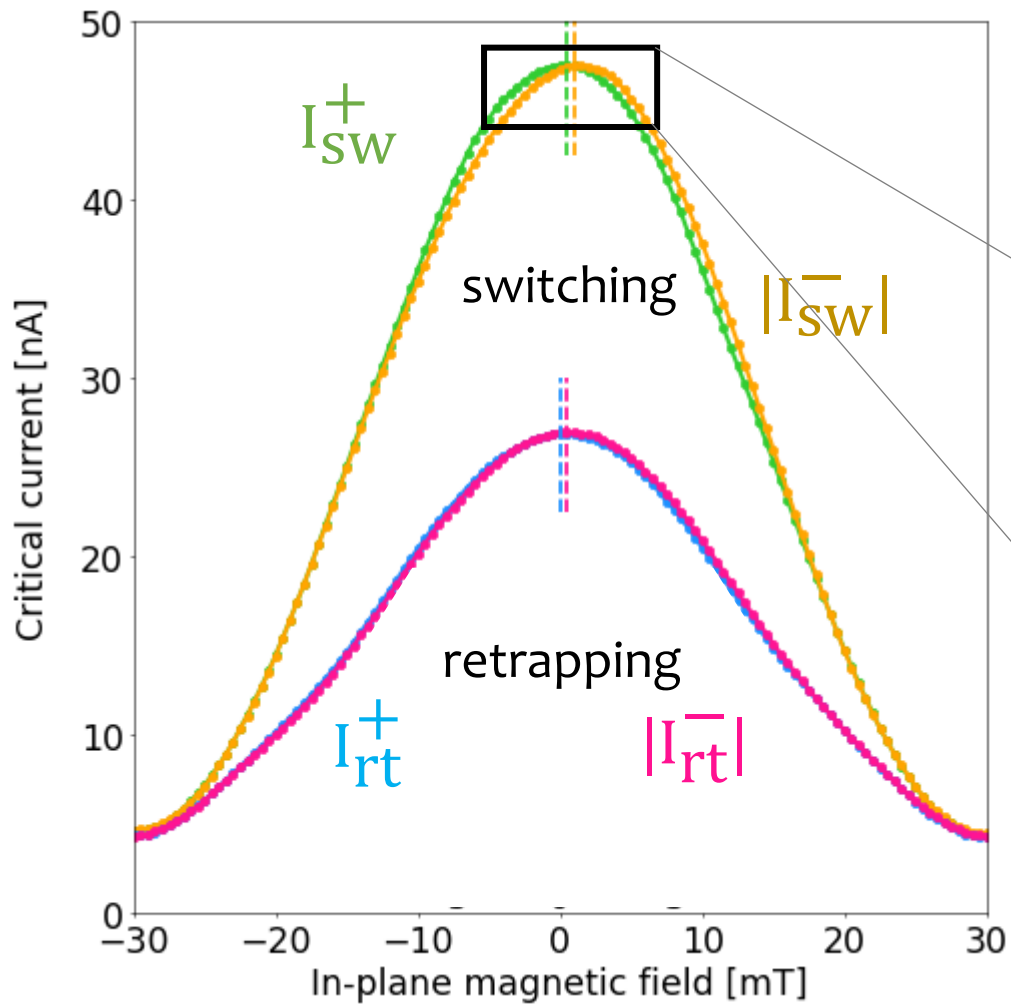
# Supercurrent at 30 mK



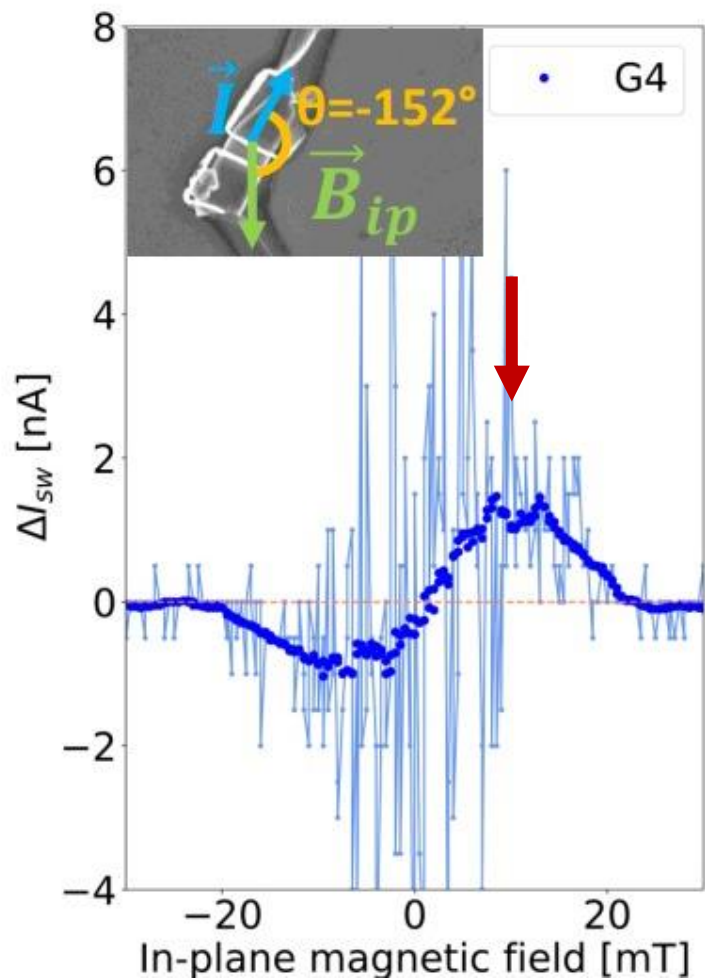
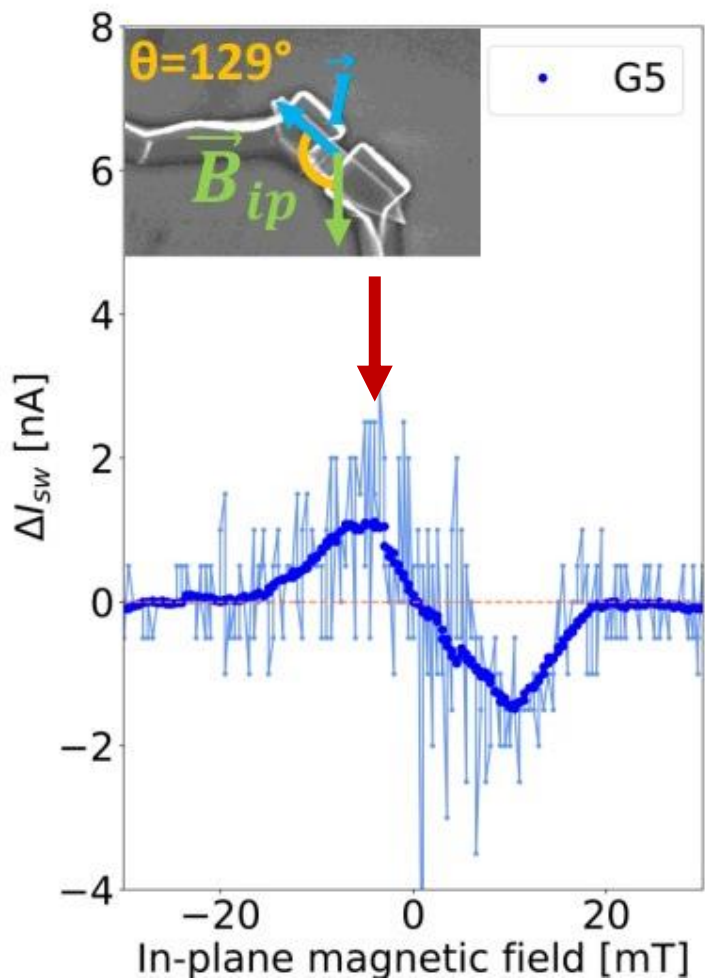
Bianca Turini



# JDE is driven by the magnetic field



# Switching current asymmetry



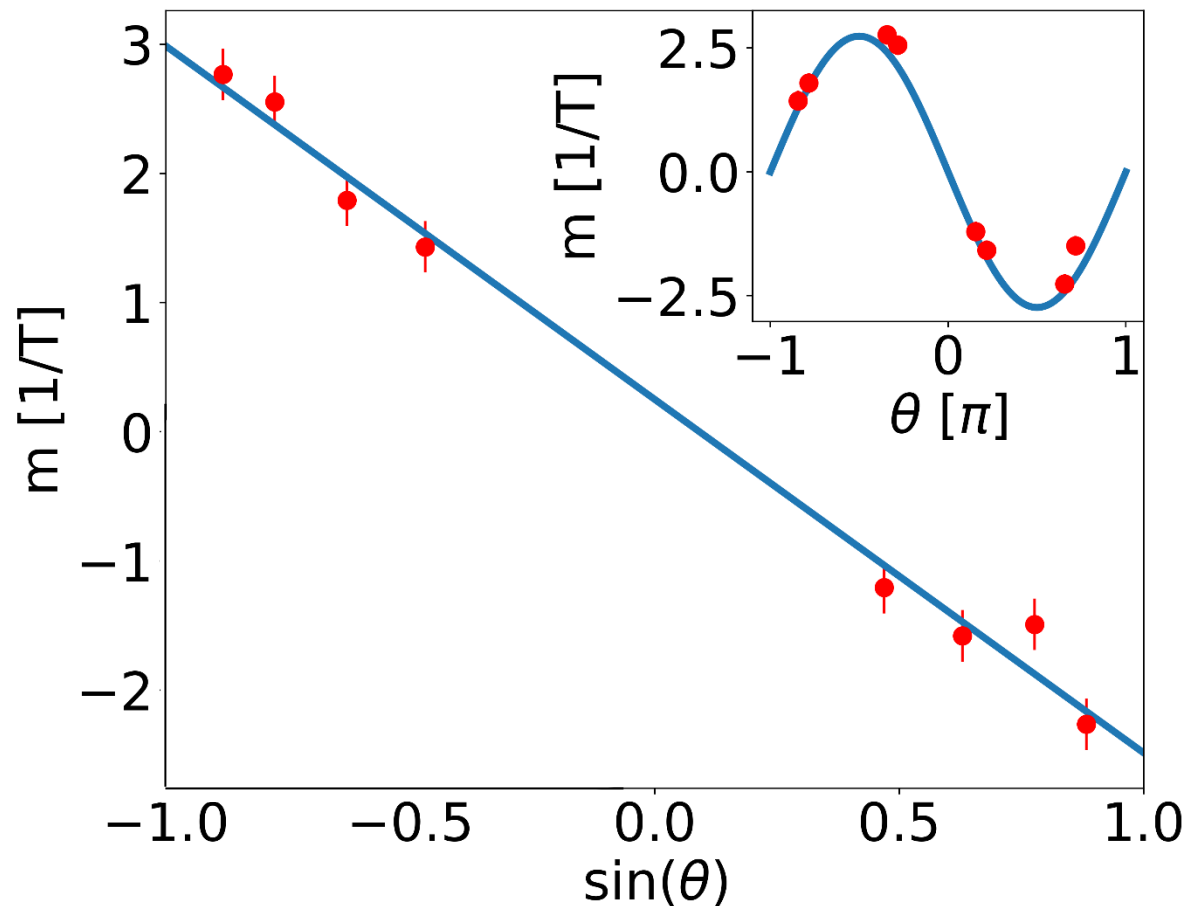
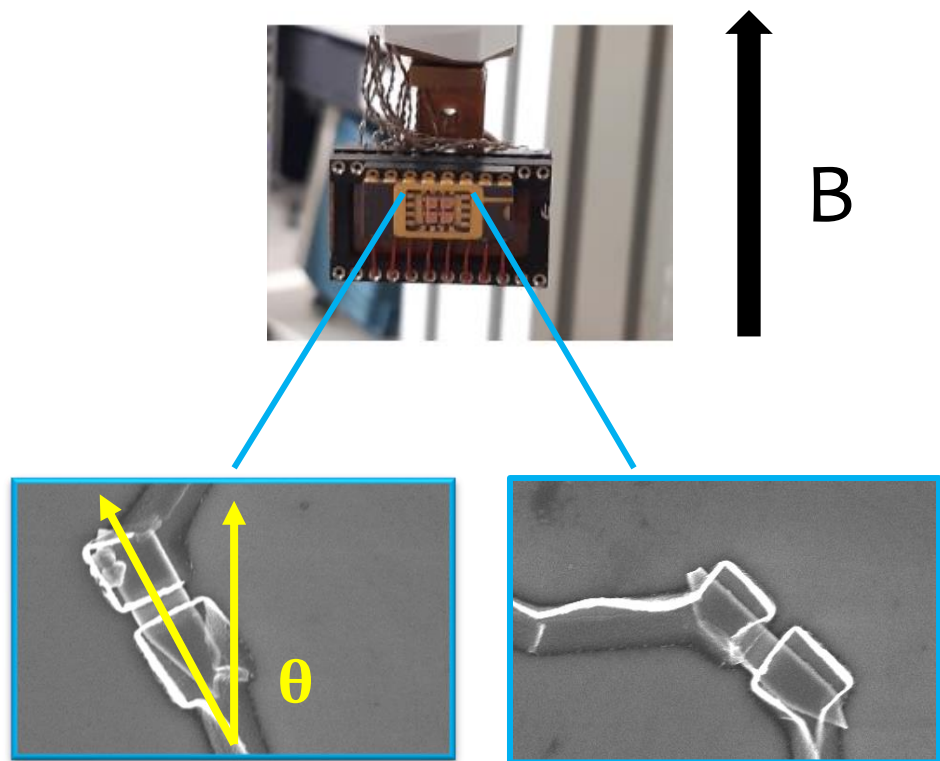
$$\Delta I_{sw} = I_{sw}^+ - |I_{sw}^-|$$

Main features:

- antisymmetric behavior
- linear around  $B = 0$
- rounded maximum
- suppression at  $B \gtrsim 20$  mT
- $\theta$ -dependent polarity

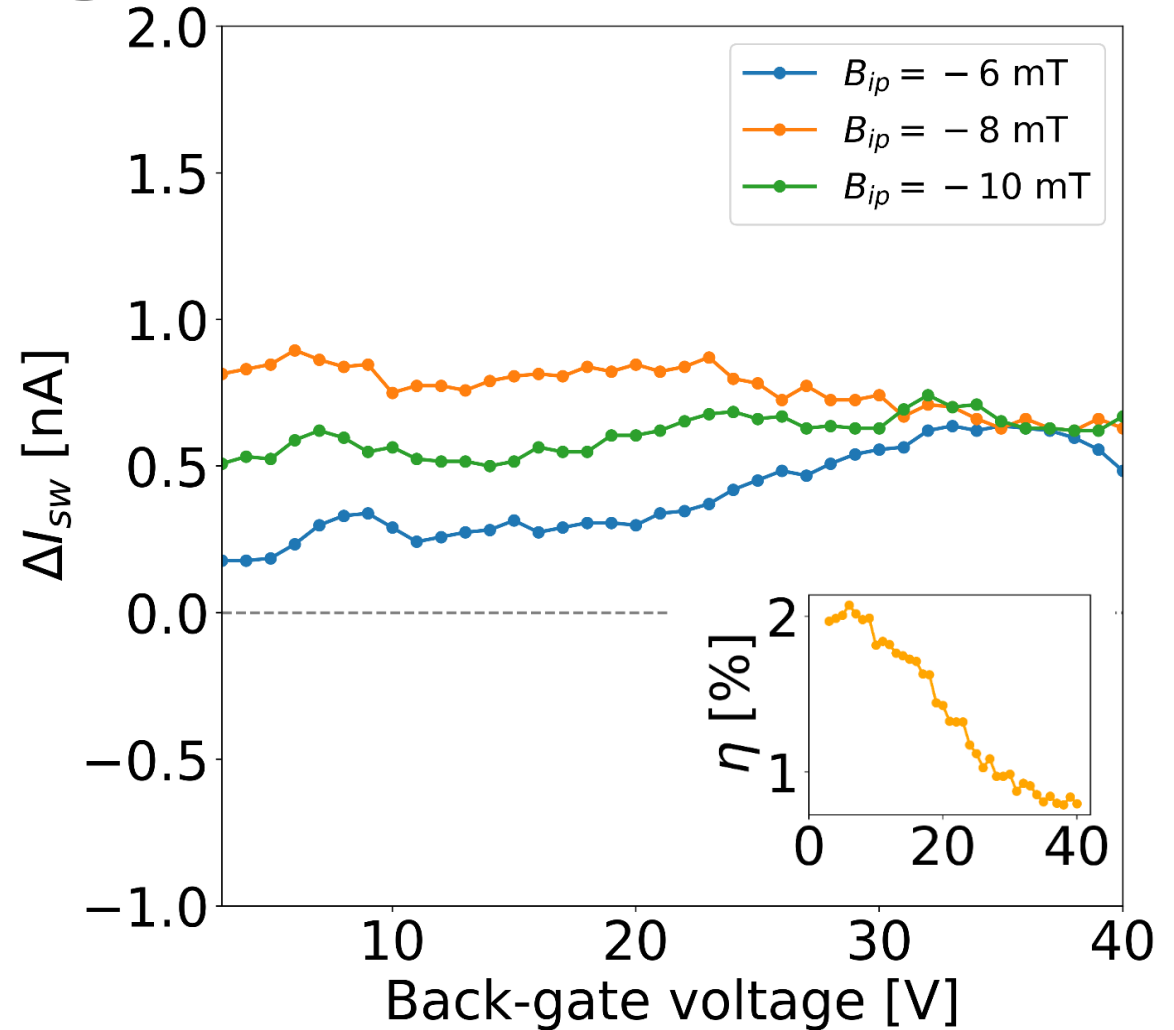
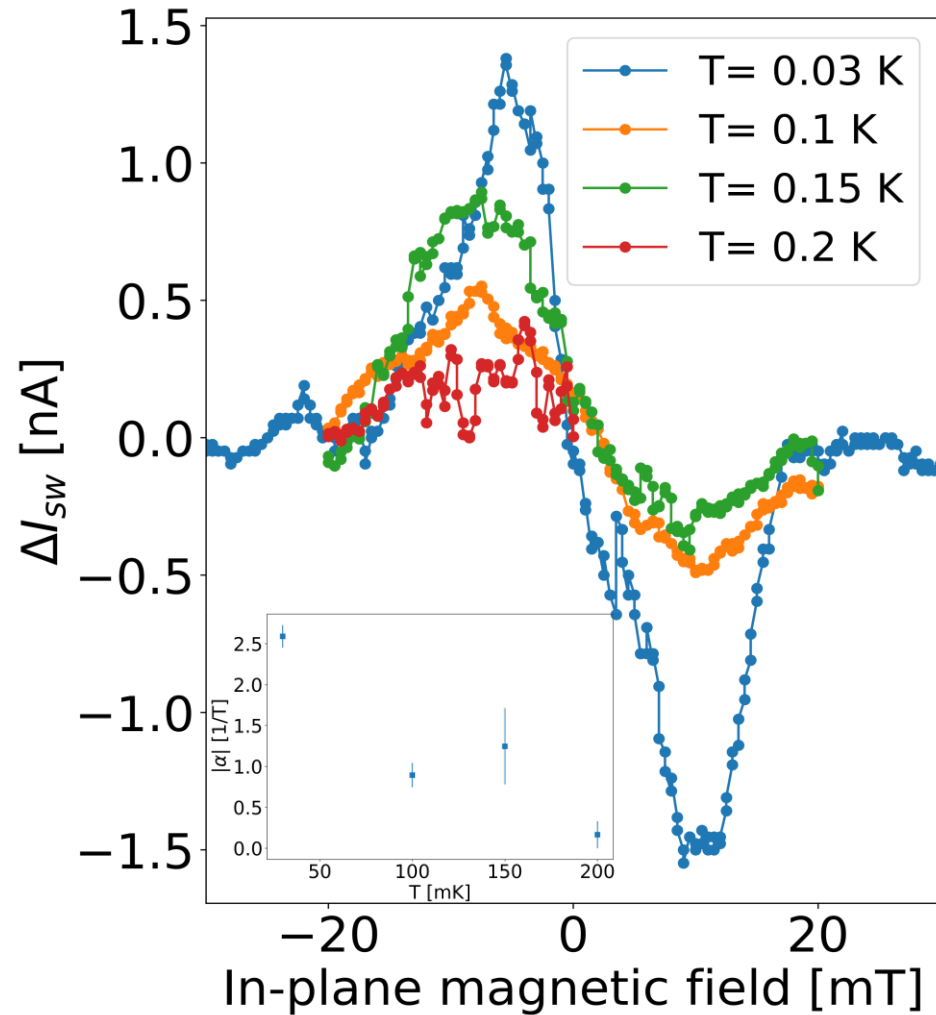
# JDE depends on the in-plane angle due to Rashba coupling

Rasmussen *et al.*, PRB (2016)



# JDE depends on temperature and back-gate voltage

$$\eta = \Delta I_{sw} / (I_C^+ + I_C^-)$$

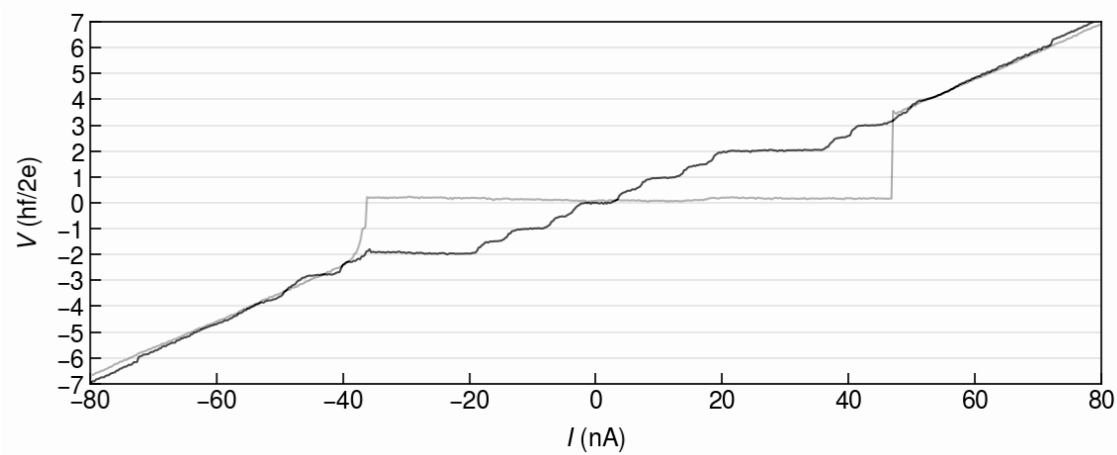
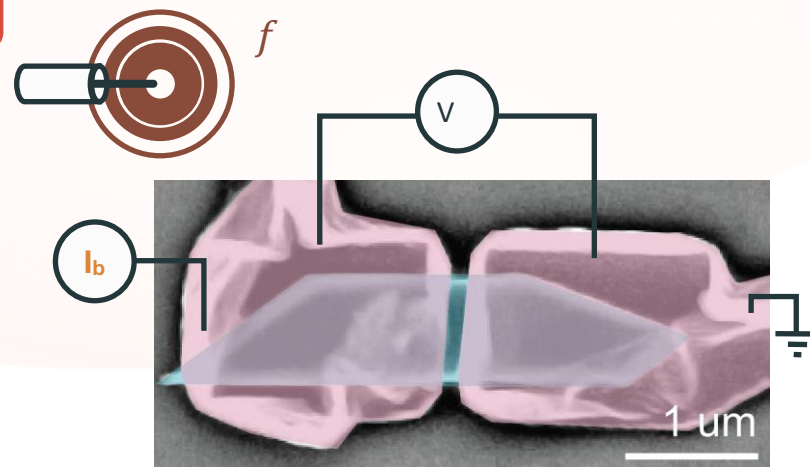




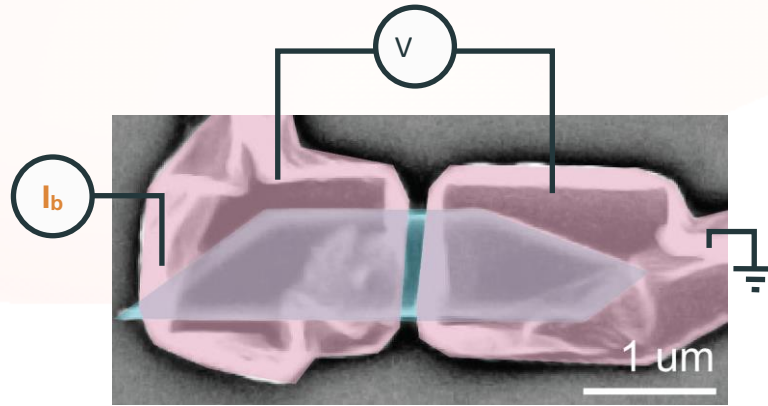
# Outline of the talk

- InSb nanoflags for advanced devices
- Nanoflag-based Josephson junctions
- Josephson diode effect in InSb nanoflags
- **Half-integer Shapiro steps in InSb nanoflags**

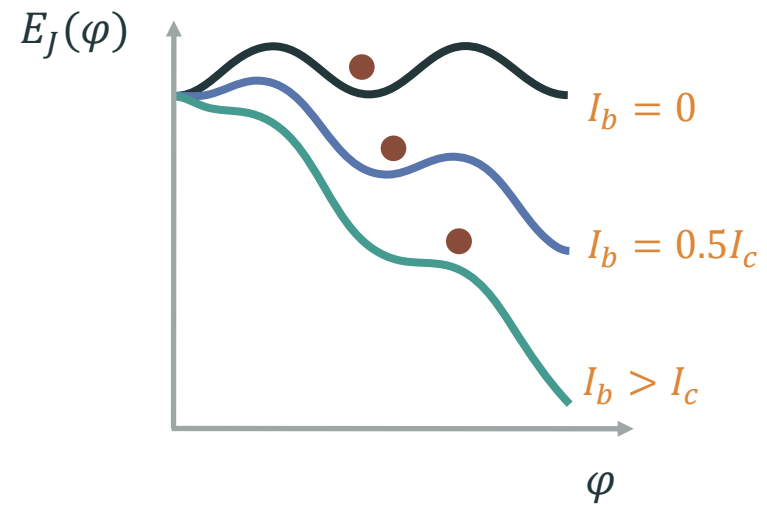
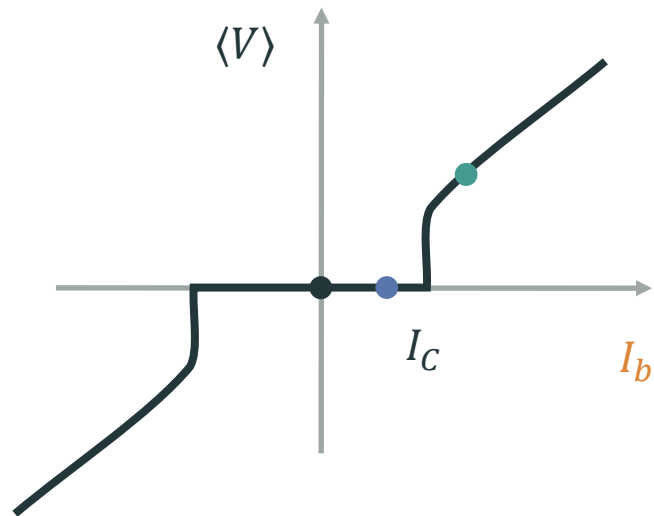
## Half-integer Shapiro steps



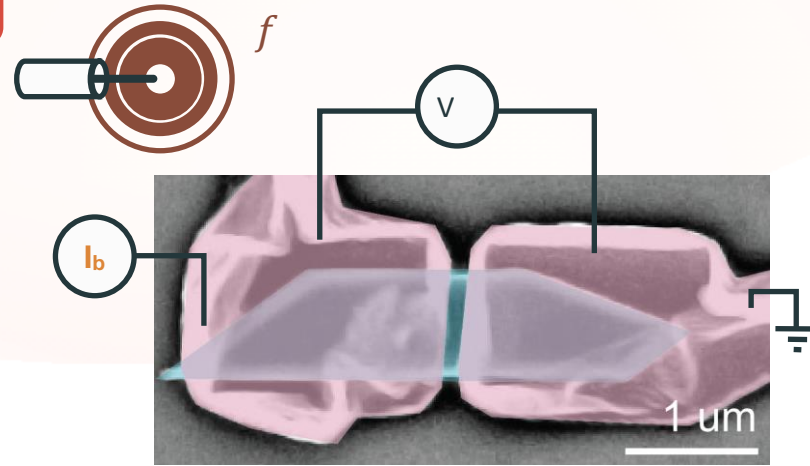
# Half-integer Shapiro steps



$$V = \frac{\hbar}{2e} \dot{\varphi}$$



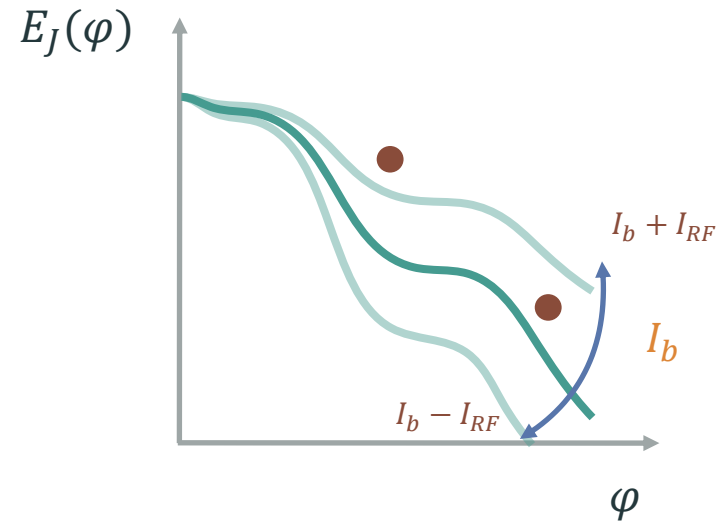
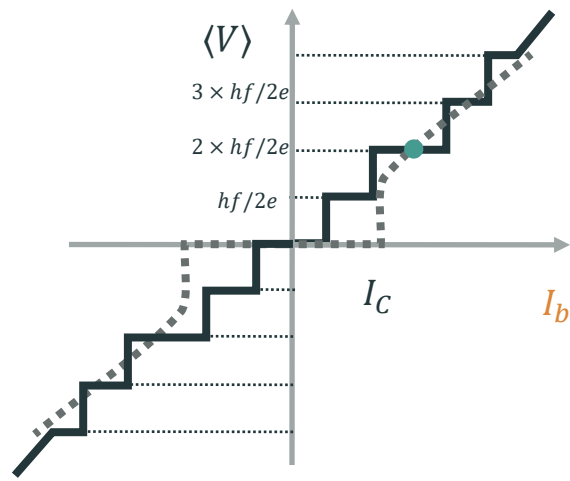
# Half-integer Shapiro steps



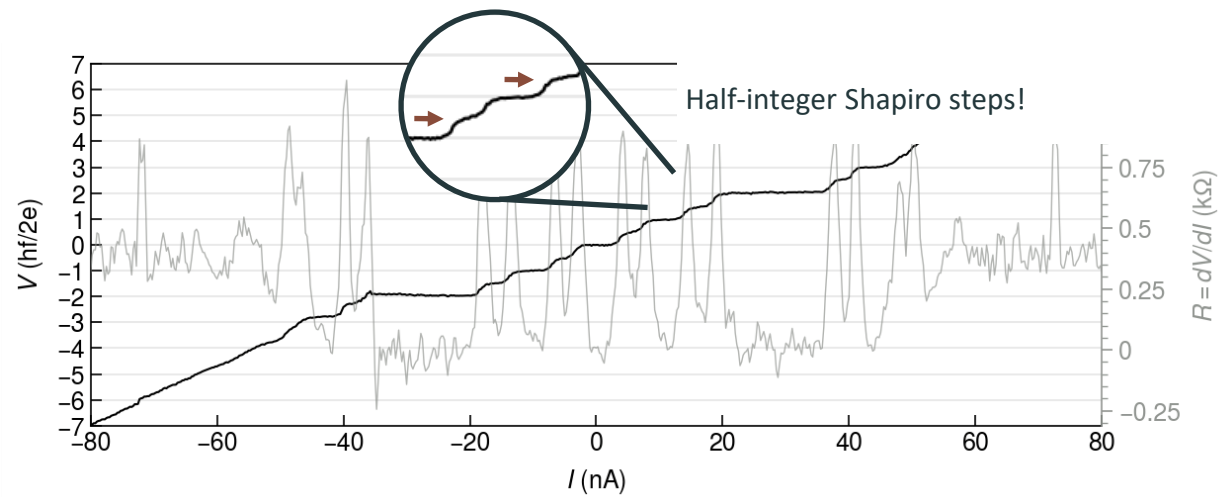
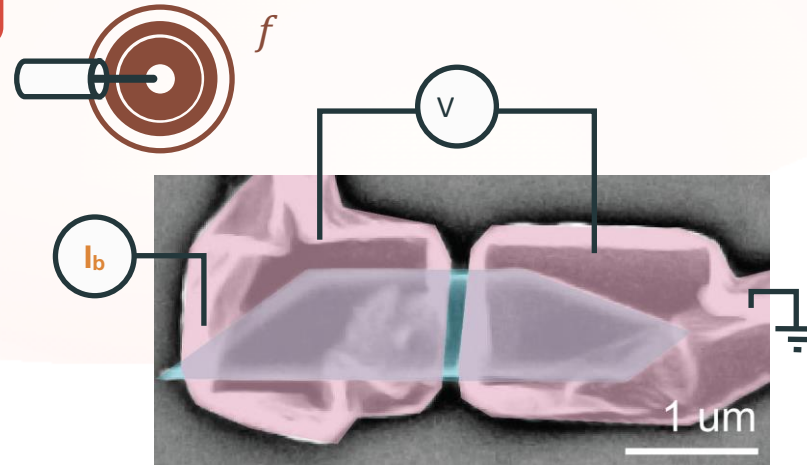
If particle rolls  $n$  minima in a period  $T = 2\pi/f$ , then  $\dot{\varphi} = 2\pi n f$

$$V = \frac{\hbar}{2e} \dot{\varphi}$$

$$= \frac{hf}{2e} n$$

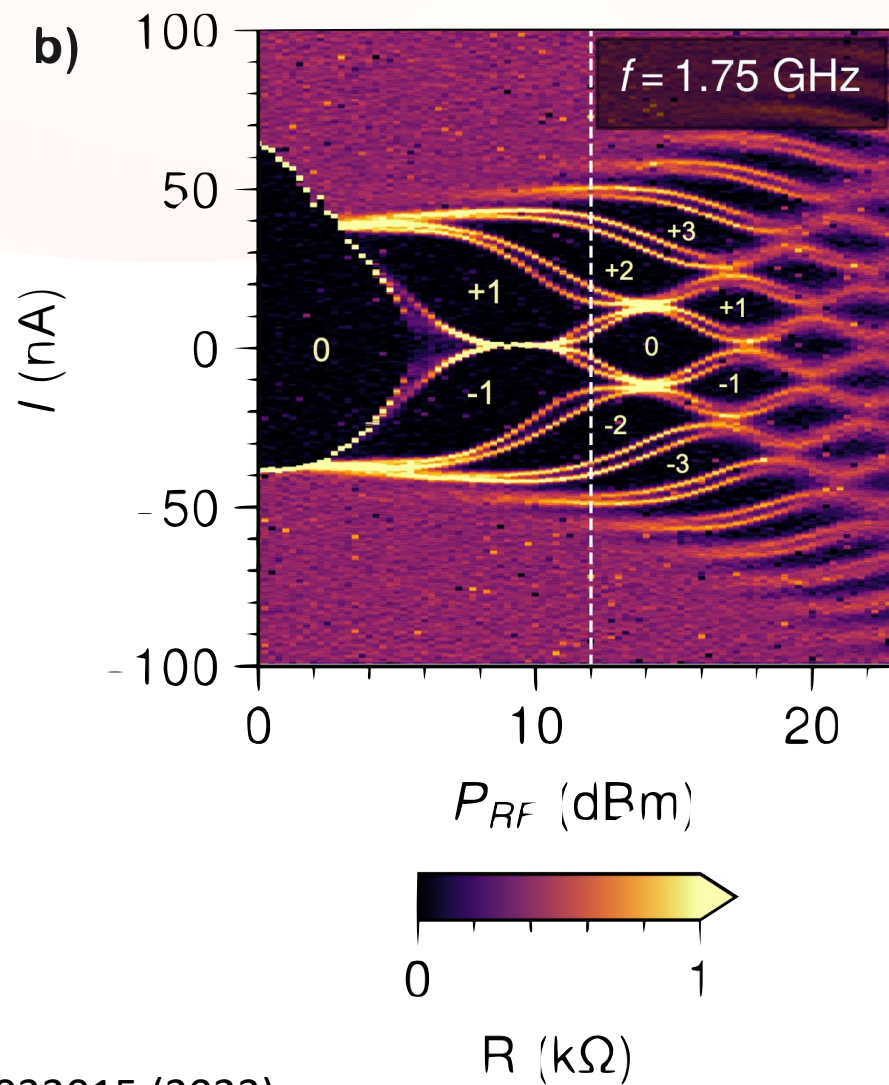


## Half-integer Shapiro steps



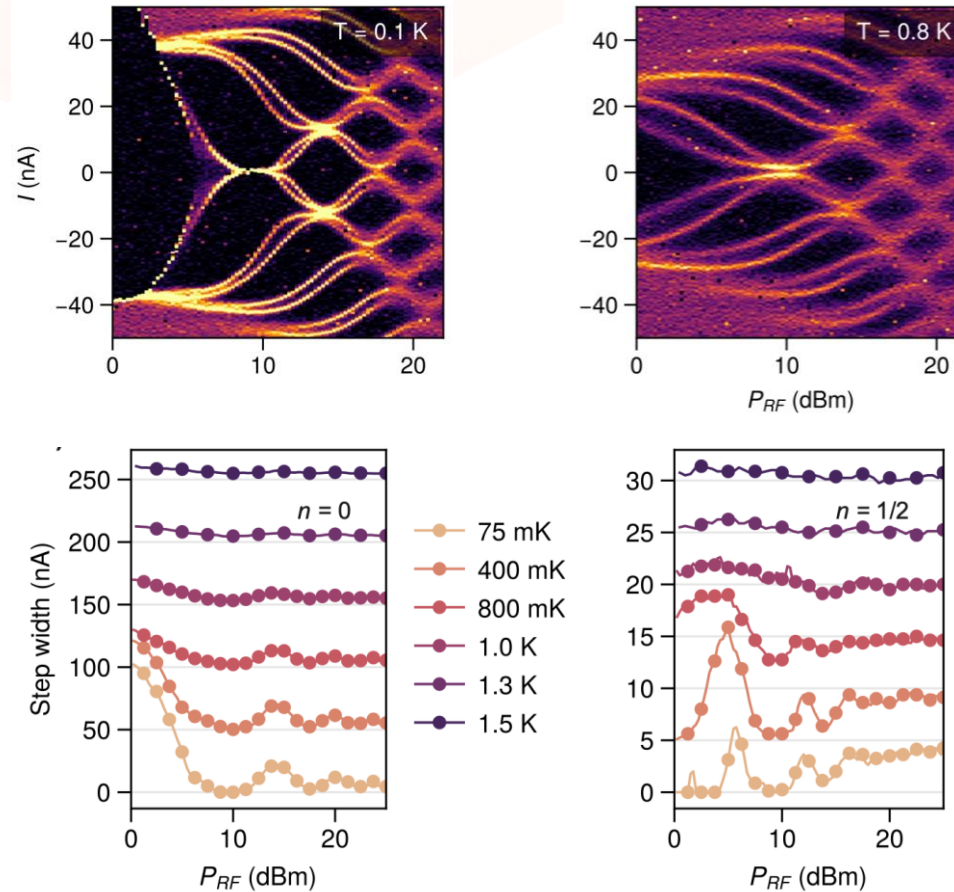
Shapiro steps – Quantized voltage plateaus  $V = \frac{hf}{2e} n$

## Half-integer Shapiro steps



# Half-integer Shapiro steps

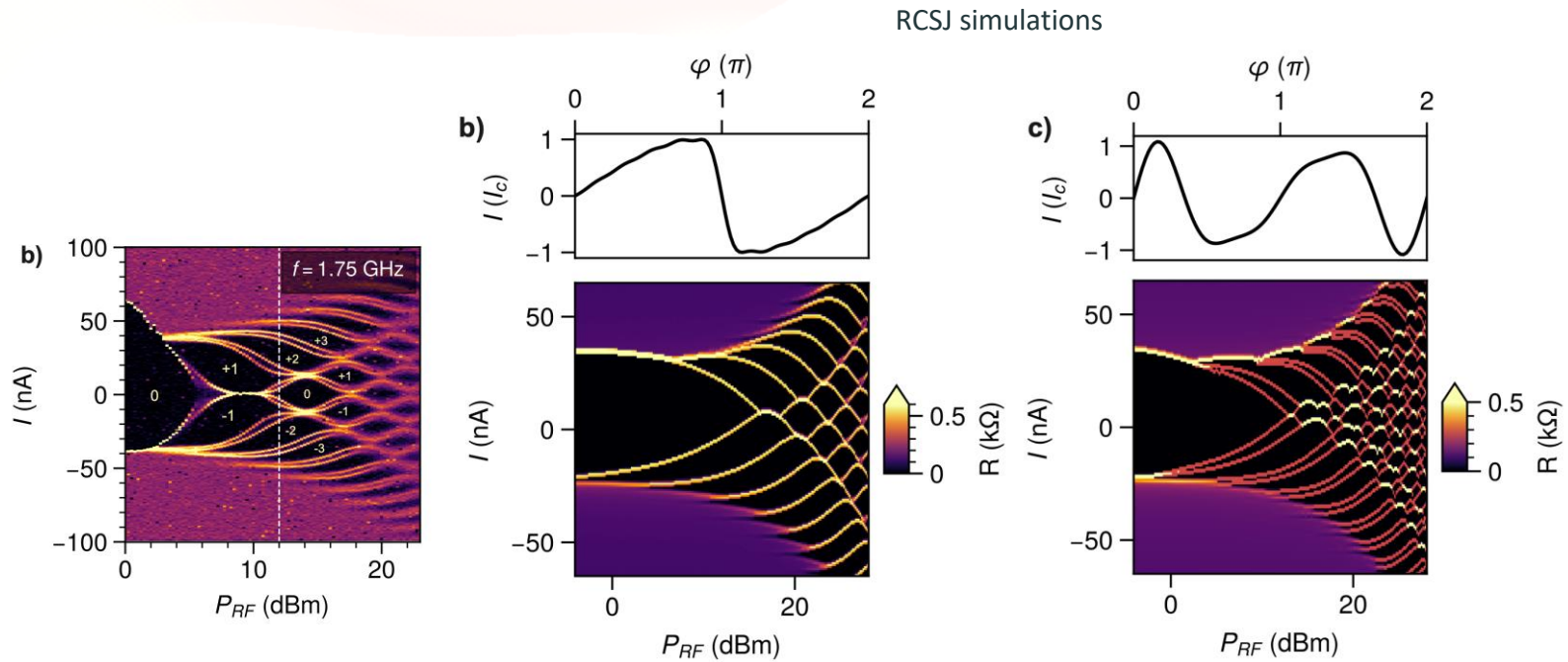
## A non-monotonic temperature dependence



# Half-integer Shapiro steps

How to have half-integer steps?

Need for a  $\sin(2\varphi)$  CPR

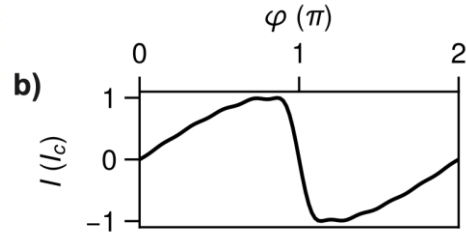




# Half-integer Shapiro steps

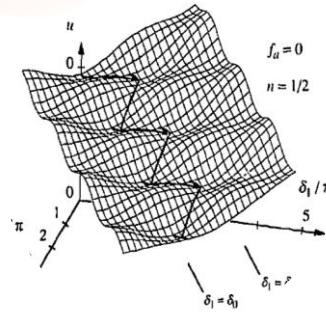
## Potential mechanisms for $\sin(2\varphi)$

Higher harmonic in the equilibrium CPR



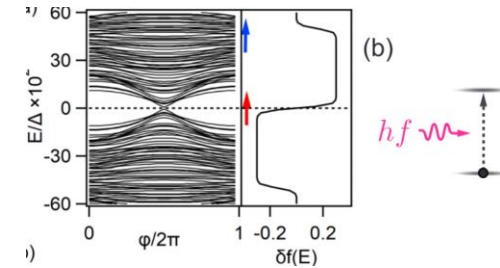
- ✓ Common given explanation
- ✗ Weaker half-steps
- ✗ Half-steps decrease with T

SQUID-like



- ✓ Robust half-steps
- ✗ Different geometry
- ✗ B-field dependent

Non-equilibrium excitations



- ✓  $\sin(2\varphi)$  only when driving
- ✓ Half-steps non-monotonic in T
- ! Still some gaps with the theory

Physical basis for half-integral Shapiro steps in a dc SQUID. Physica C: Superconductivity 245.3-4 (1995)

Theory of microwave-assisted supercurrent in quantum point contacts. Physical review letters 105.11 (2010)  
 Microwave photoassisted dissipation and supercurrent of a phase-biased graphene-superconductor ring. Physical Review Research 3.3 (2021)

# Half-integer Shapiro steps

## Almost four contemporary papers

March 10, 2023

### Half-integer Shapiro steps in highly transmissive InSb nanoflag Josephson junctions

A. Iorio<sup>1,\*</sup>, A. Crippa<sup>1</sup>, B. Turini<sup>1,†</sup>, S. Salimian<sup>1</sup>, M. Carrega<sup>2</sup>, L. Chirolli<sup>1</sup>, V. Zannier<sup>1</sup>, L. Sorba<sup>1</sup>,  
E. Strambini<sup>1</sup>, F. Giazotto<sup>1</sup> and S. Heun<sup>1,‡</sup>

April 23, 2023

### Large Second-Order Josephson Effect in Planar Superconductor-Semiconductor Junctions

P. Zhang<sup>1</sup>, A. Zarassi<sup>1</sup>, L. Jarjat<sup>2</sup>, V. Van de Sande<sup>3</sup>, M. Pendharkar<sup>4</sup>, J.S. Lee<sup>5</sup>, C.P. Dempsey<sup>4</sup>, A.P. McFadden<sup>4</sup>,  
S.D. Harrington<sup>6</sup>, J.T. Dong<sup>6</sup>, H. Wu<sup>1</sup>, A.-H. Chen<sup>7</sup>, M. Hocevar<sup>7</sup>, C.J. Palmström<sup>4,5,6</sup> and S.M. Frolov<sup>1,\*</sup>

June 8, 2023

### Charge-4e supercurrent in an InAs-Al superconductor-semiconductor heterostructure

Carlo Ciaccia<sup>1,\*</sup>, Roy Haller<sup>1</sup>, Asbjørn C. C. Drachmann<sup>2,3</sup>, Tyler Lindemann<sup>4,5</sup>,  
Michael J. Manfra<sup>4,5,6,7</sup>, Constantin Schrade<sup>2</sup> and Christian Schönenberger<sup>1,8</sup>

June 12, 2023

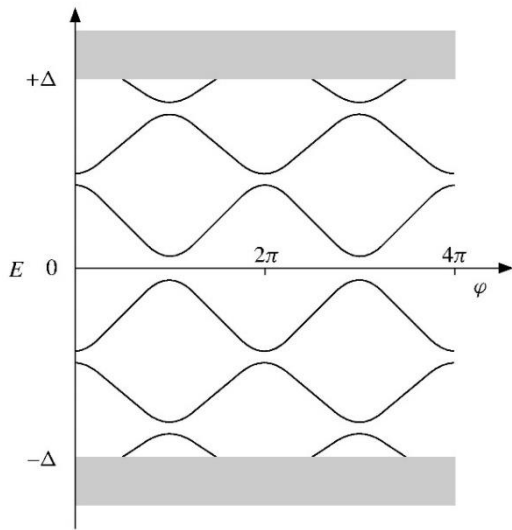
### Radio frequency driven superconducting diode and parity conserving Cooper pair transport in a two-dimensional germanium hole gas

Marco Valentini<sup>1,\*</sup>, Oliver Sagi<sup>1</sup>, Levon Baghumyan<sup>1</sup>, Thijs de Gijzel<sup>1,2</sup>, Jason Jung<sup>2</sup>, Stefano Calcaterra<sup>3</sup>,  
Andrea Ballabio<sup>3</sup>, Juan Aguilera Servin<sup>1</sup>, Kushagra Aggarwal<sup>1,4</sup>, Marian Janik<sup>1</sup>, Thomas Adletzberger<sup>1</sup>,  
Rubén Seoane Souto<sup>5,6</sup>, Martin Leijnse<sup>7</sup>, Jeroen Danon<sup>8</sup>, Constantin Schrade<sup>5</sup>, Erik Bakkers<sup>2</sup>,  
Daniel Chrastina<sup>3</sup>, Giovanni Isella<sup>3</sup>, Georgios Katsaros<sup>1,\*</sup>

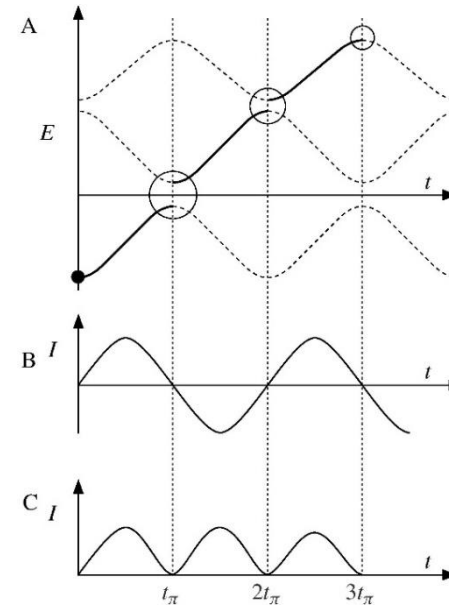
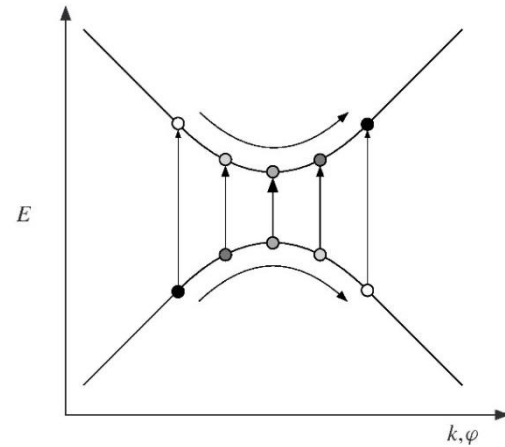
23

# Half-integer Shapiro steps (non-equilibrium)

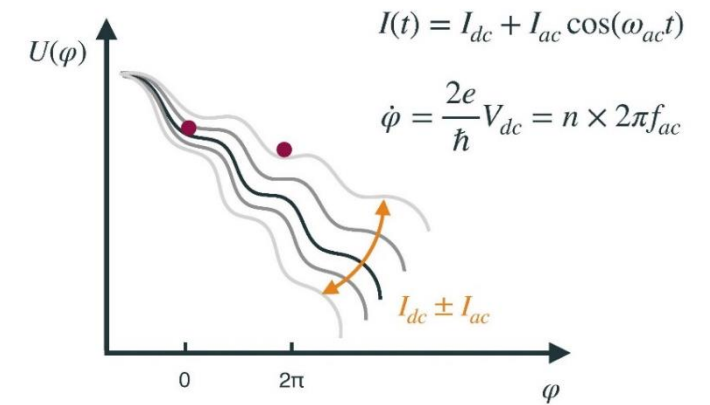
- Non-equilibrium occupation probability of Andreev Bound States
  - Strong  $2\varphi$ -periodic oscillations at twice the Josephson frequency
  - Giving rise to half-integer Shapiro-steps



Schematic Andreev Bands



$$I = \frac{2e}{\hbar} \cdot \frac{dE}{d\varphi}$$



$$\text{Josephson frequency } \omega_J = \frac{d\varphi}{dt} = \frac{2eV}{\hbar}$$

H. Kroemer, Superlattices and Microstructures 25 (1999) 877.

# Outlook: gate-controlled SOI

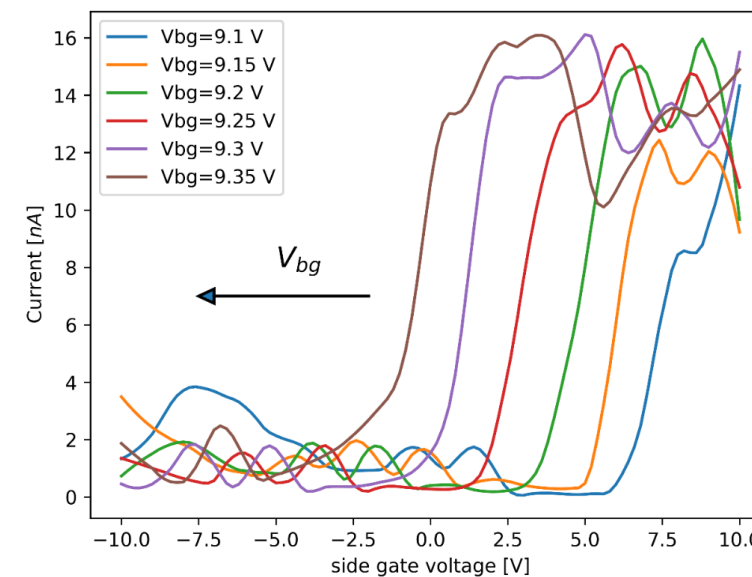
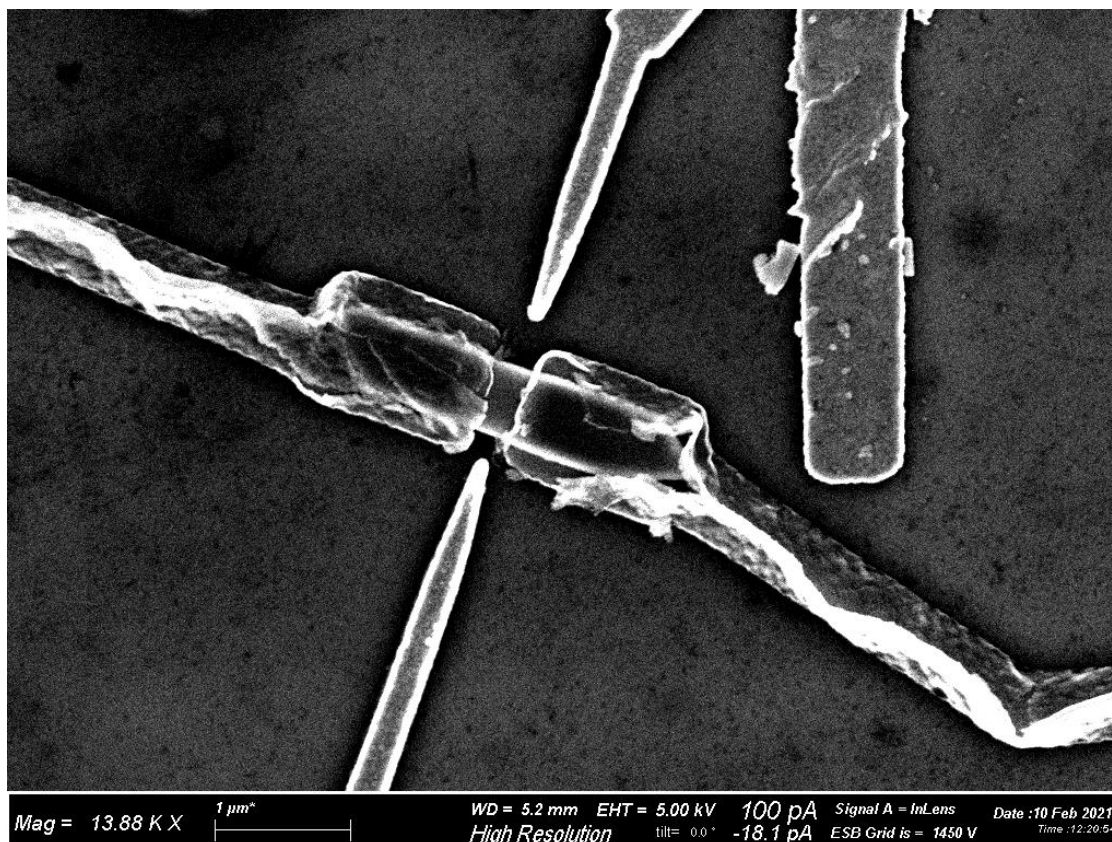
**Idea:** tune the effective geometry and the SO coupling with side gates



Bianca Turini

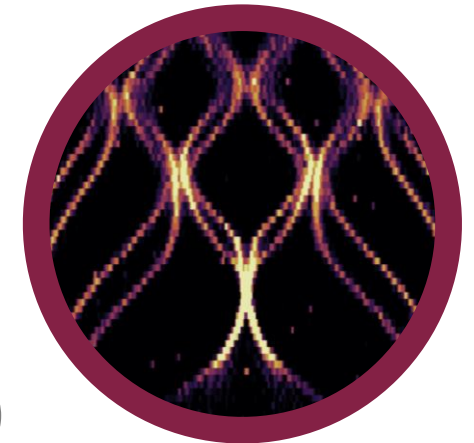
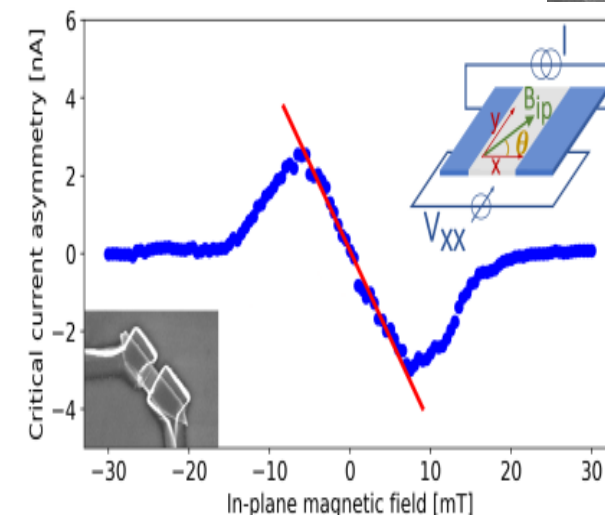
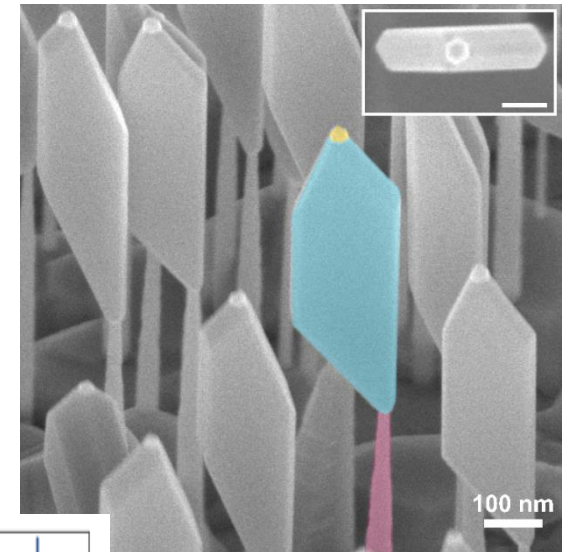
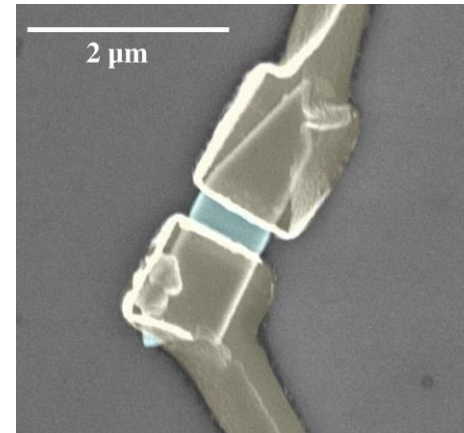


Federico Paolucci



# Summary

- Free-standing 2D InSb nanoflags via CBE:
  - Defect-free zinc blende crystal structures
  - High-mobility devices
- InSb nanoflag-based Josephson junctions:
  - High-transparency of the interfaces
  - Ballistic transport
  - Gate-controlled supercurrent
- Josephson diode effect:
  - First observation of the JDE in InSb
  - Magnetic field-driven rectification
  - Relevance of Rashba SOC in the system
- Half-integer Shapiro steps:
  - Shapiro steps are still an open-topic in SNS devices
  - Controllable manipulation of bound states excitations (Andreev qubits)



# People Involved

## *Growth activity*



Isha Verma



Valentina  
Zannier



Lucia Sorba



Sedighe Salimian



Matteo Carrega  
Luca Chirolli

## *Devices*

## *Theory*

## Acknowledgments:



## *Transport*



Bianca Turini



Andrea Iorio



Alessandro  
Crippa



Elia Strambini



Francesco Giazotto

# Postdoc Position Available

- We are looking for a postdoc for the ongoing work on these InSb nanoflags.
- Mainly device fabrication and low-temperature magneto-transport.
- Please contact me: Stefan Heun ([stefan.heun@nano.cnr.it](mailto:stefan.heun@nano.cnr.it))



Thank you for your attention!